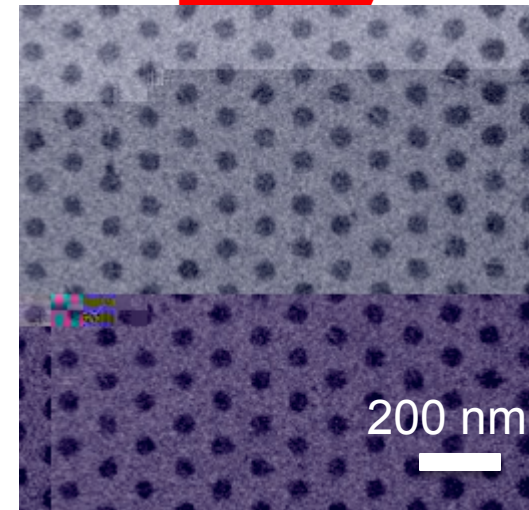
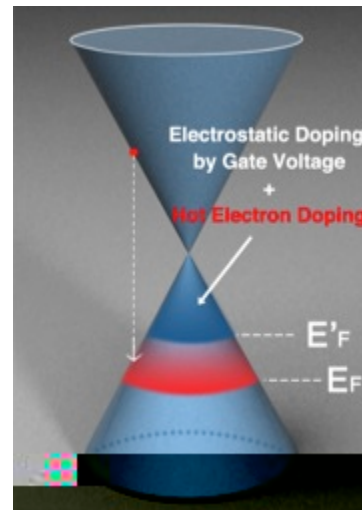
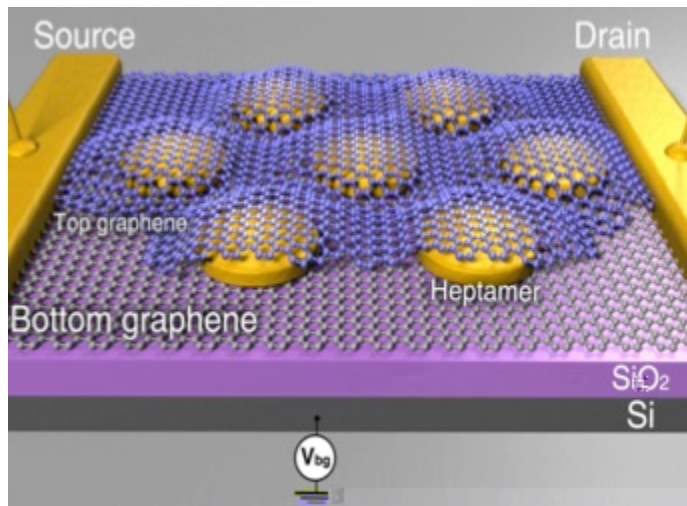


Graphene Plasmonics



Sukosin Thongrattanasiri (CSIC), Zheng Liu, Yumin Wang, Andie Schlattmann, Frank Koppens (ICFO),
F. Javier García de Abajo (CSIC), Pulickel M. Ajayan, Peter Nordlander and Naomi J. Halas



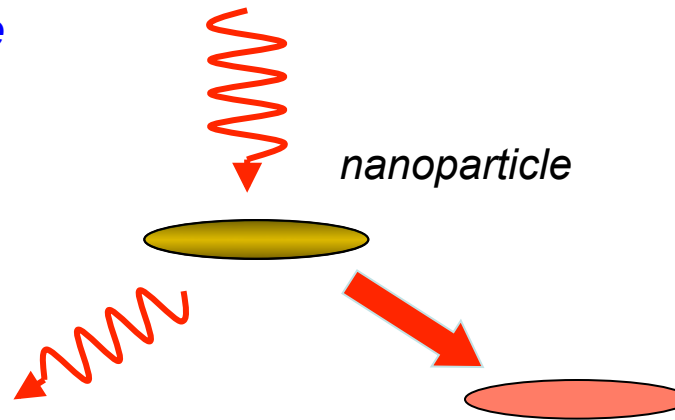
@
A + 12-16, 2012



The plasmon life cycle

Plasmonics:

Surface plasmons are collective oscillations of conduction electrons



a.k.a. radiative decay

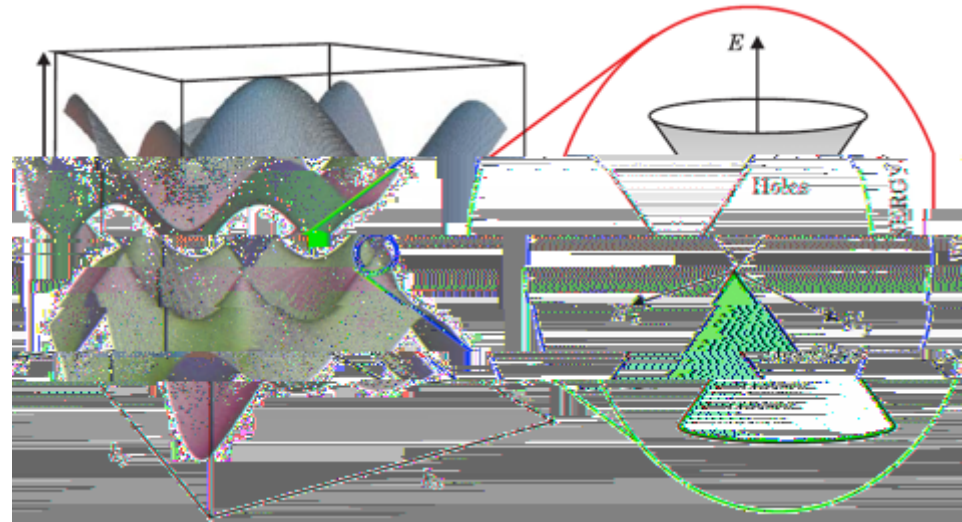
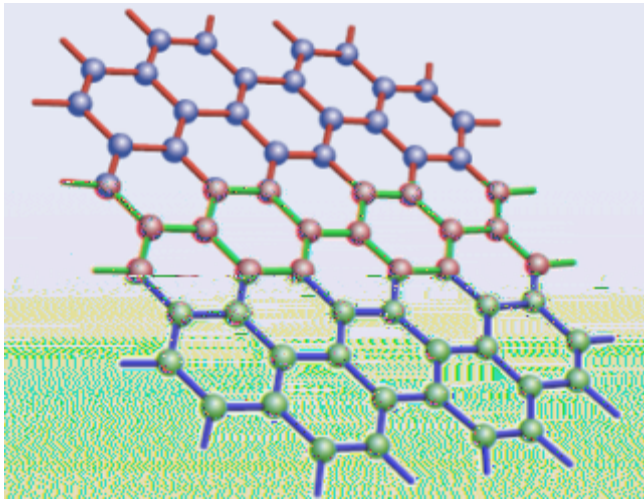
A
'hot' electron-hole pair production

C
c

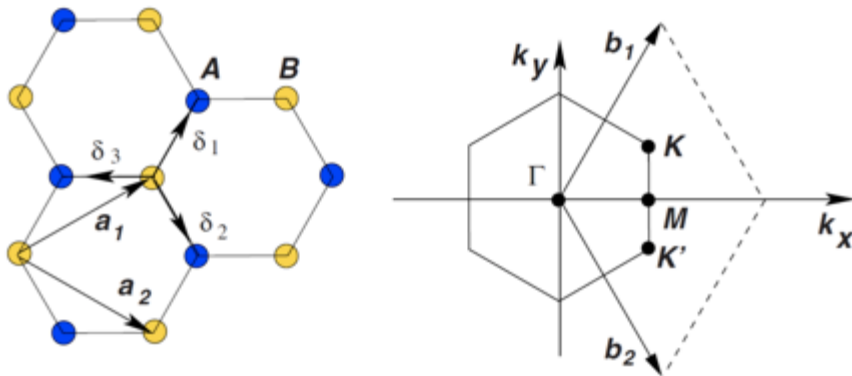
(
-
,
-
,
...)

Graphene

A flat monolayer of carbon atoms tightly packed into a 2-dimensional honeycomb lattice



Das Sarma et. al, Rev. Mod. Phys. 2011



Castro Neto et. al, Rev. Mod. Phys. 2009

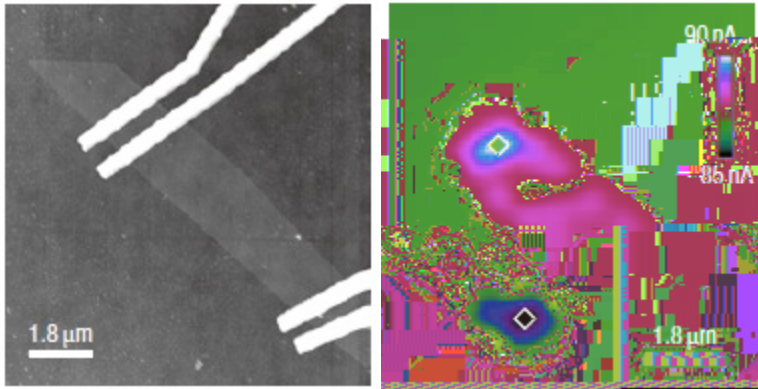
- High Mobility: $10000 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$
- Zero band gap semiconductor
- Poor absorption in visible range

- Improve graphene device optical properties in visible and NIR
- Study graphene semi-metal properties in mid- or far- infrared

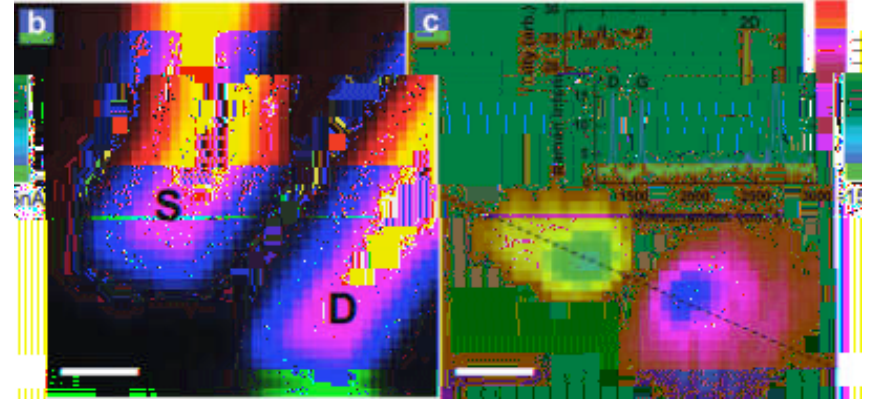
Outline

- G

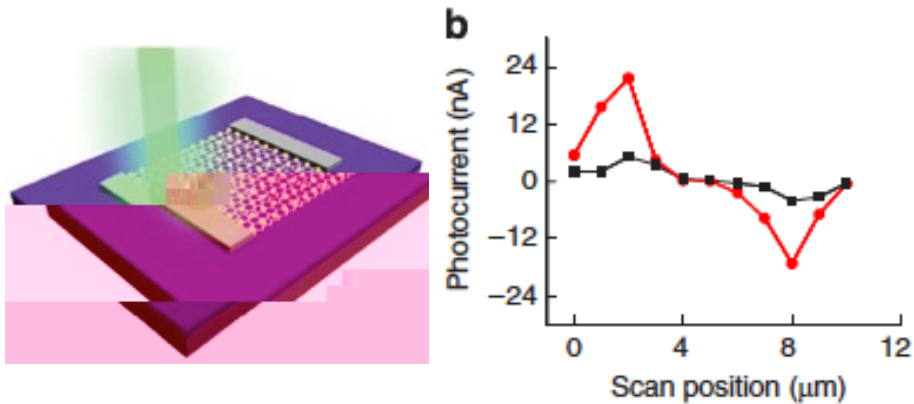
Graphene Photodetector



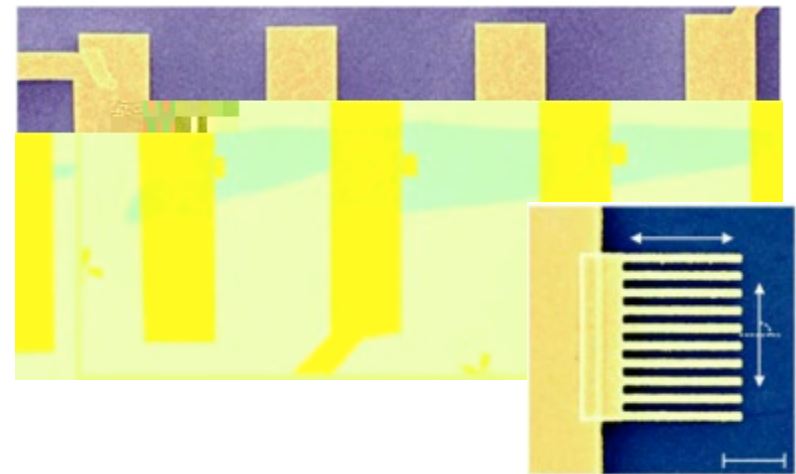
E.J.Lee et.al. *Nature Nano.*,**3**, 488 (2008)



F.Xia et.al. *Nano Lett.*,**9**,1039 (2009)

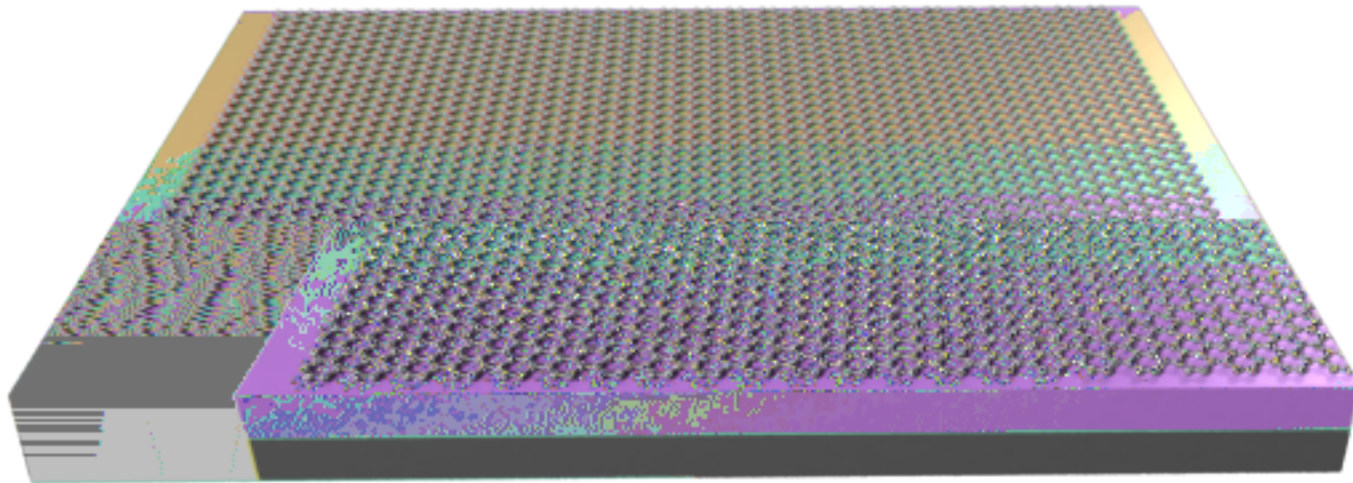


X. Duan et.al. *Nature Comm.*,**2**, 579 (2011)



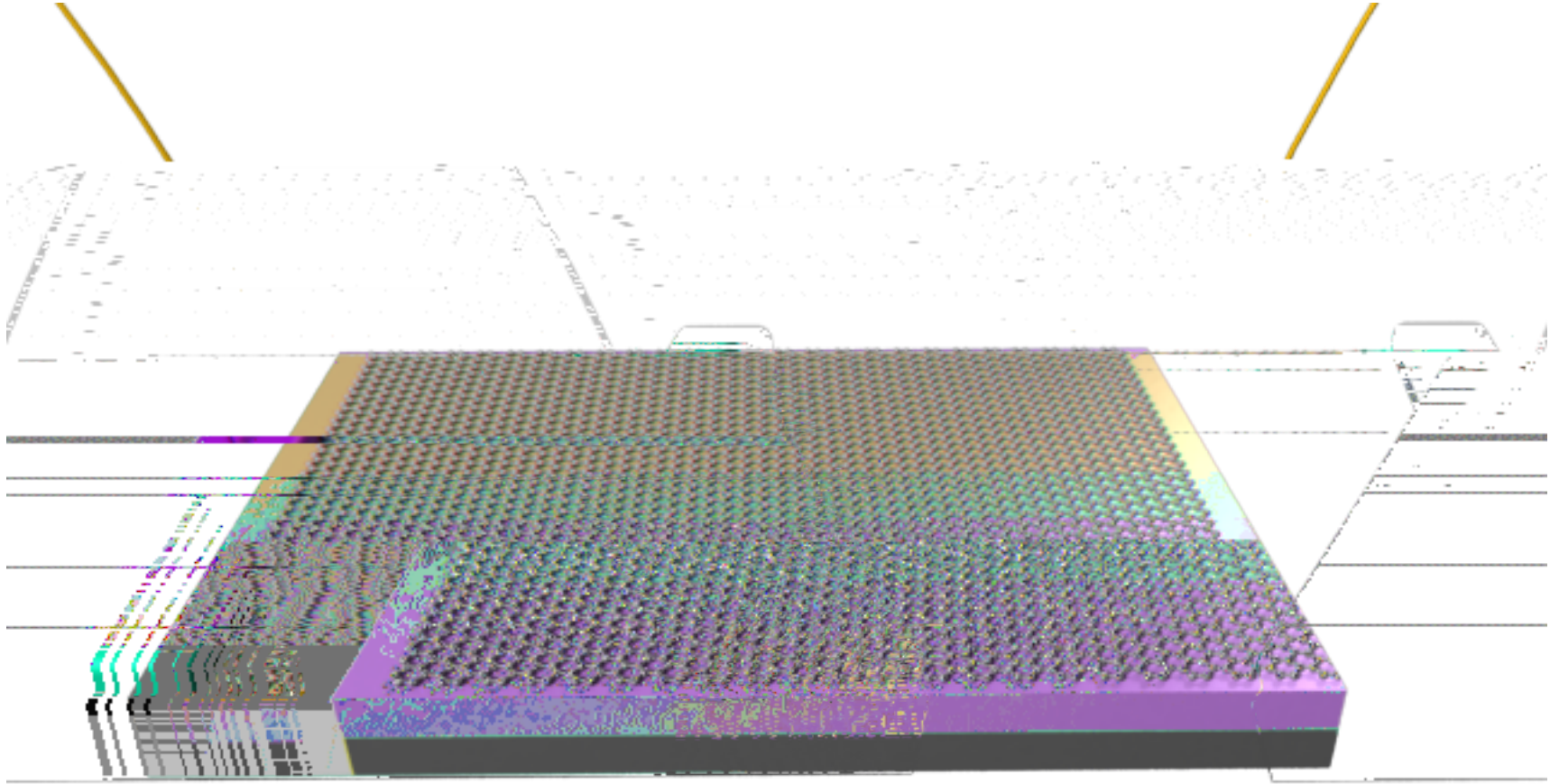
E.J.Lee et.al. *Nature Comm.*,**2**, 458 (2011)

Graphene-Antenna Sandwich Device



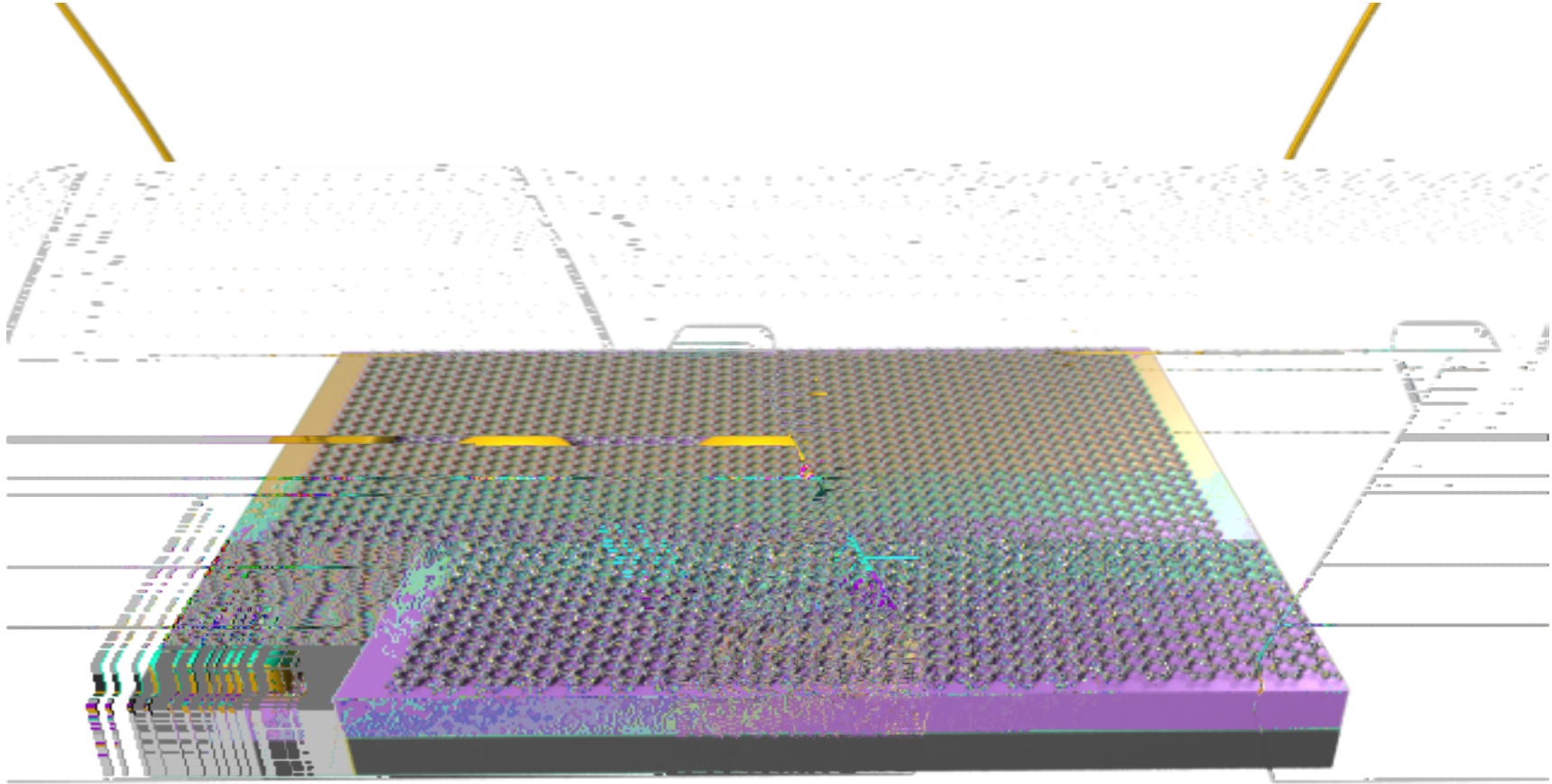
Transfer a graphene monolayer onto a SiO₂/Si substrate

Graphene-Antenna Sandwich Device



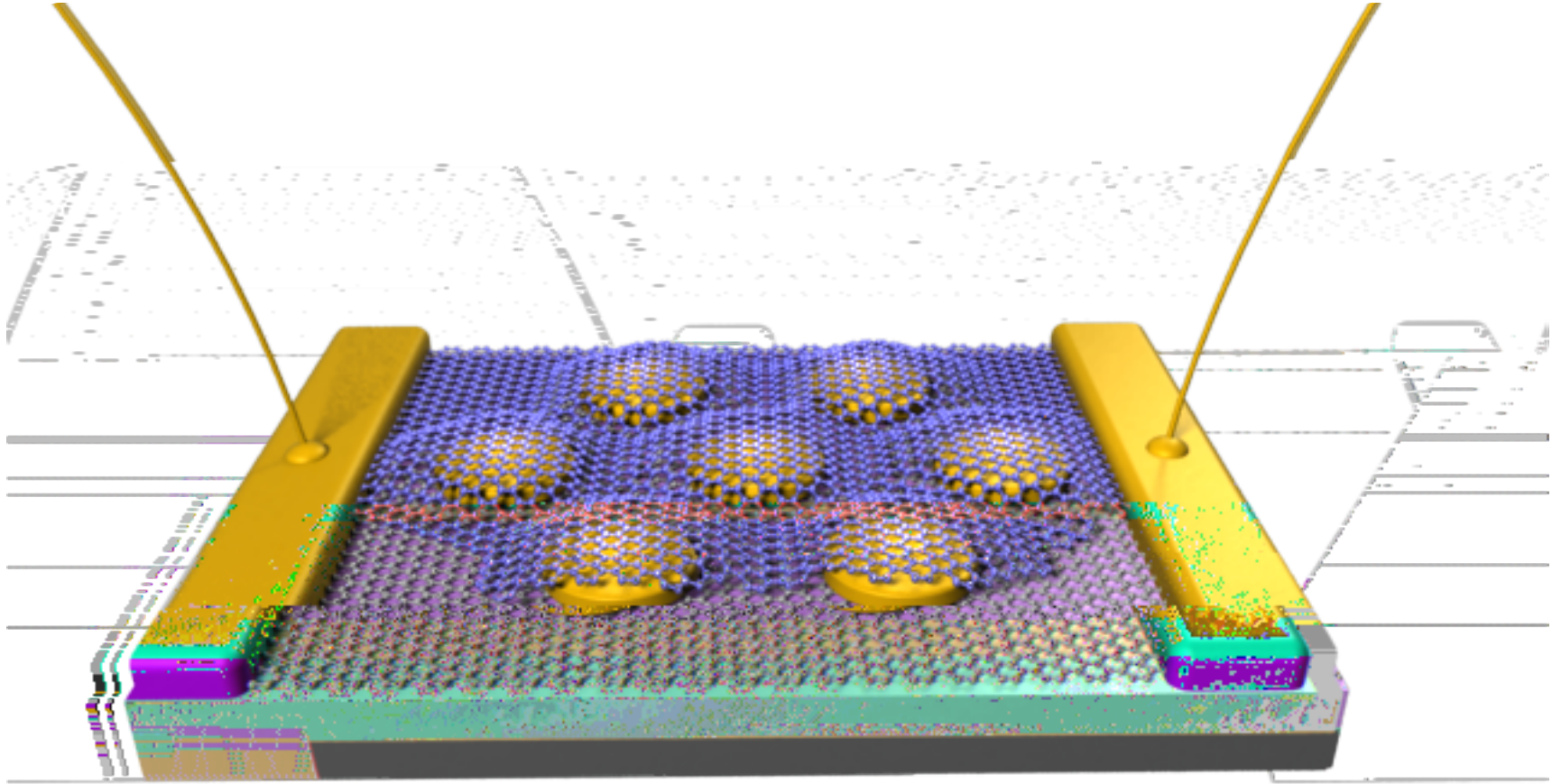
Deposit the source-drain electrodes on the graphene

Graphene-Antenna Sandwich Device



Fabricate heptamer array using two-step E-beam lithography

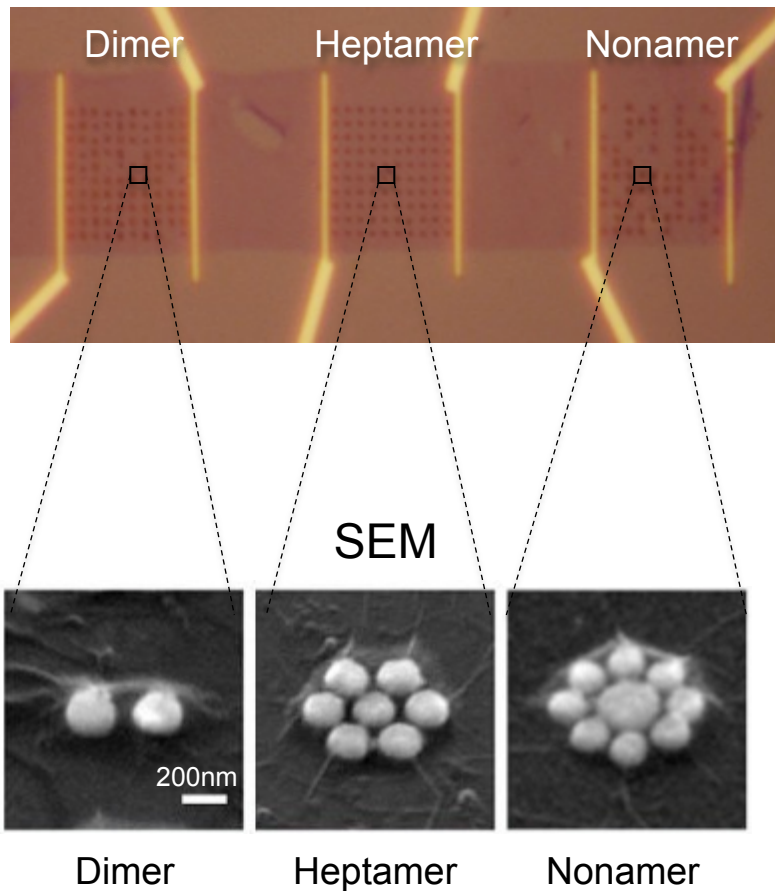
Graphene-Antenna Sandwich Device



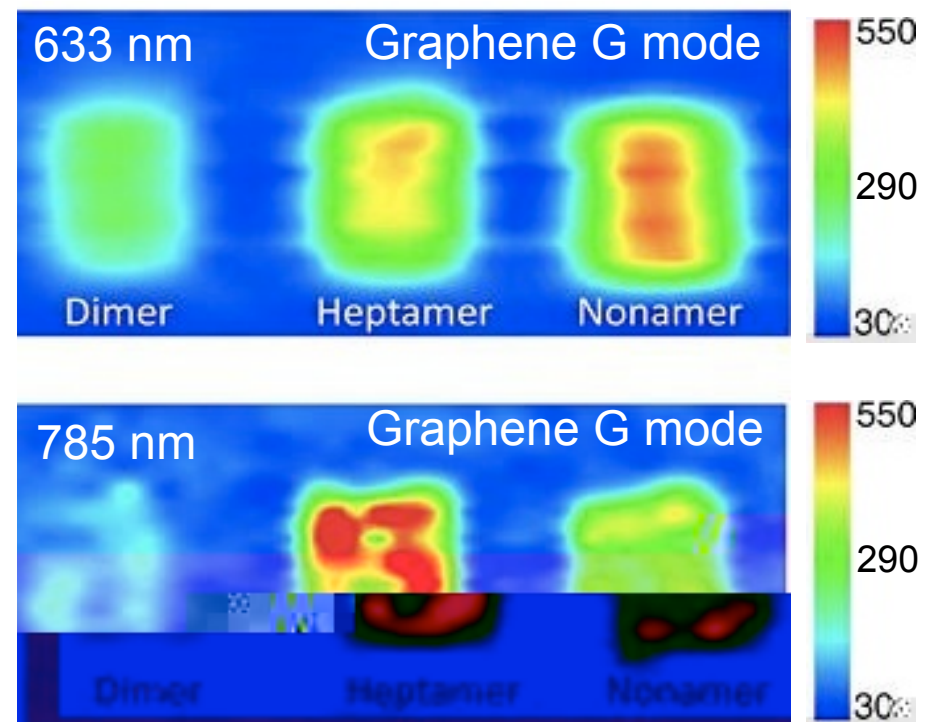
Transfer a second graphene monolayer onto the structure to form a sandwich device

Sandwich Device Characterization

Optical image of the device

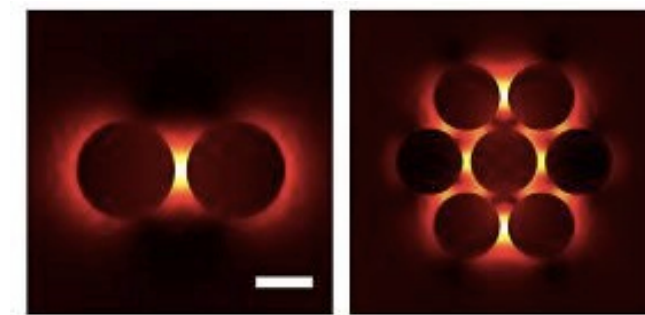
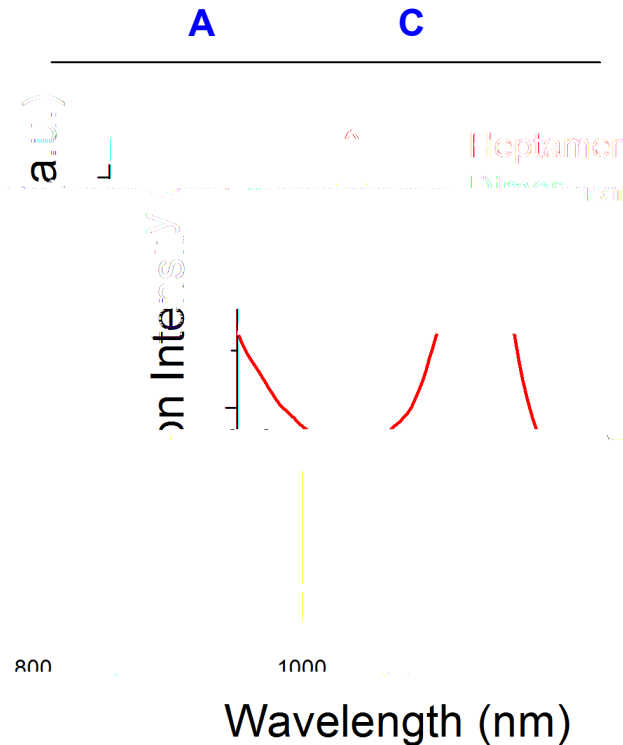
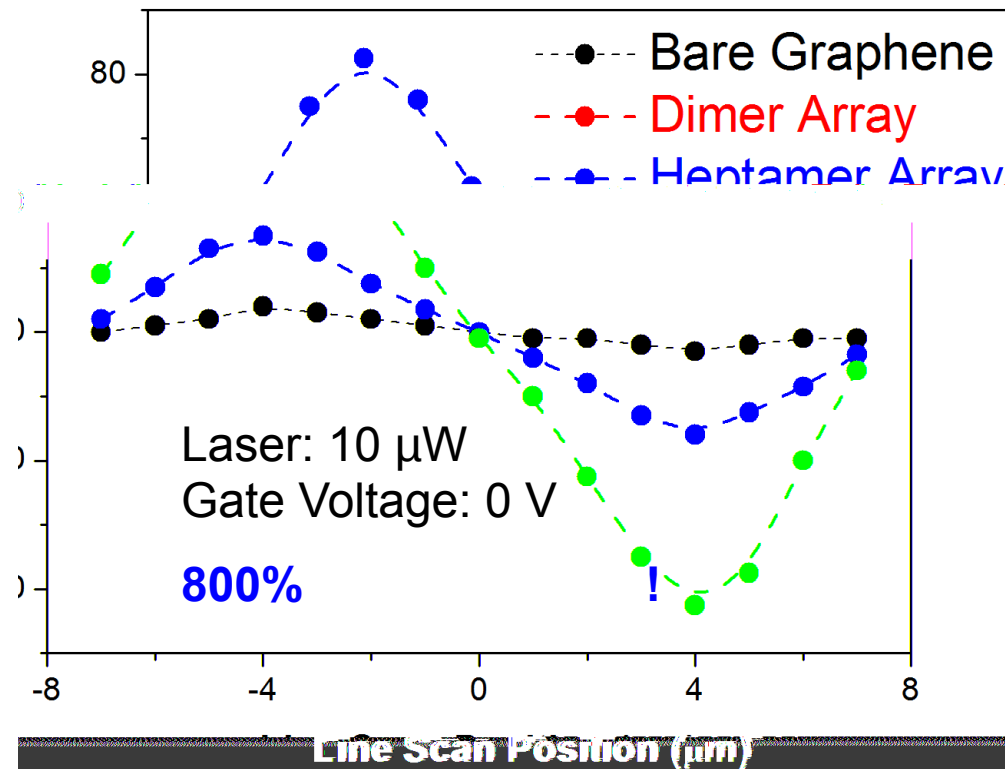
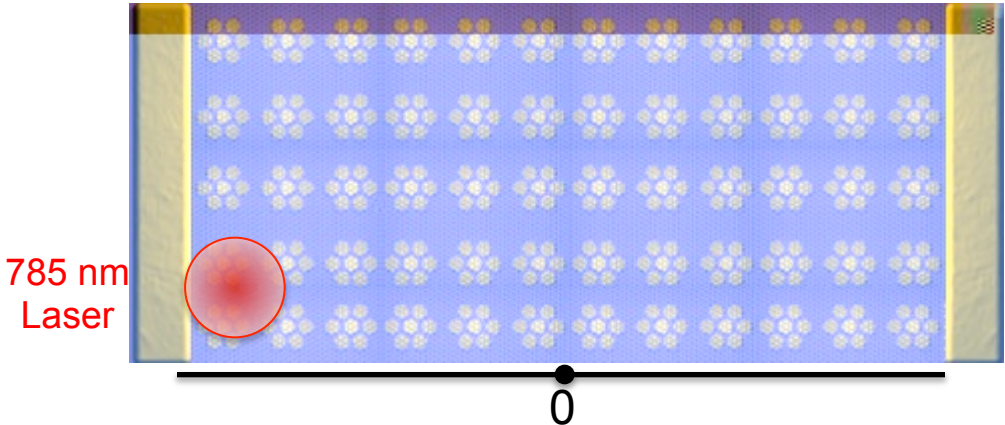


Raman mapping

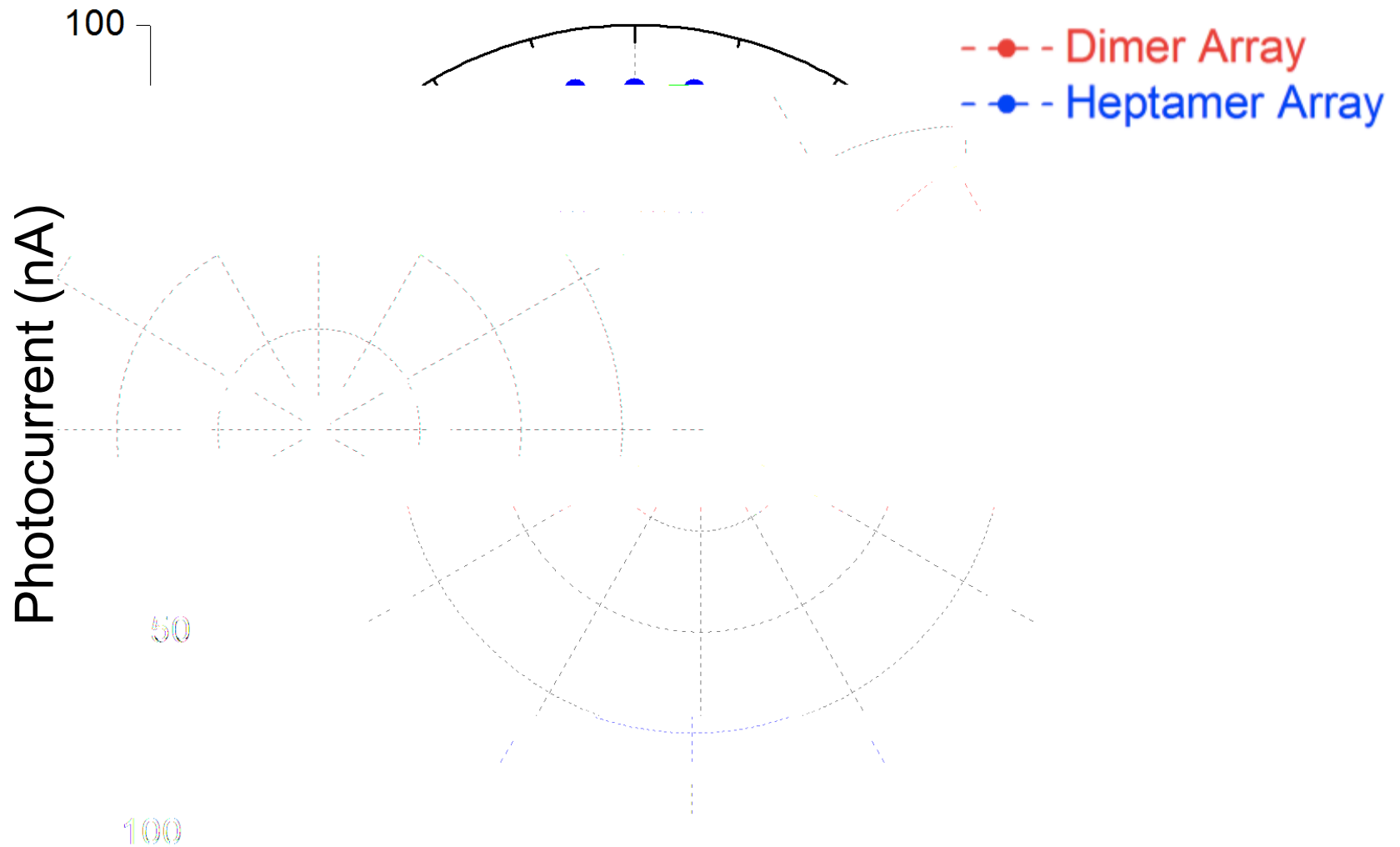


Second graphene on the top is used to capture the hot electrons from the whole k -space !

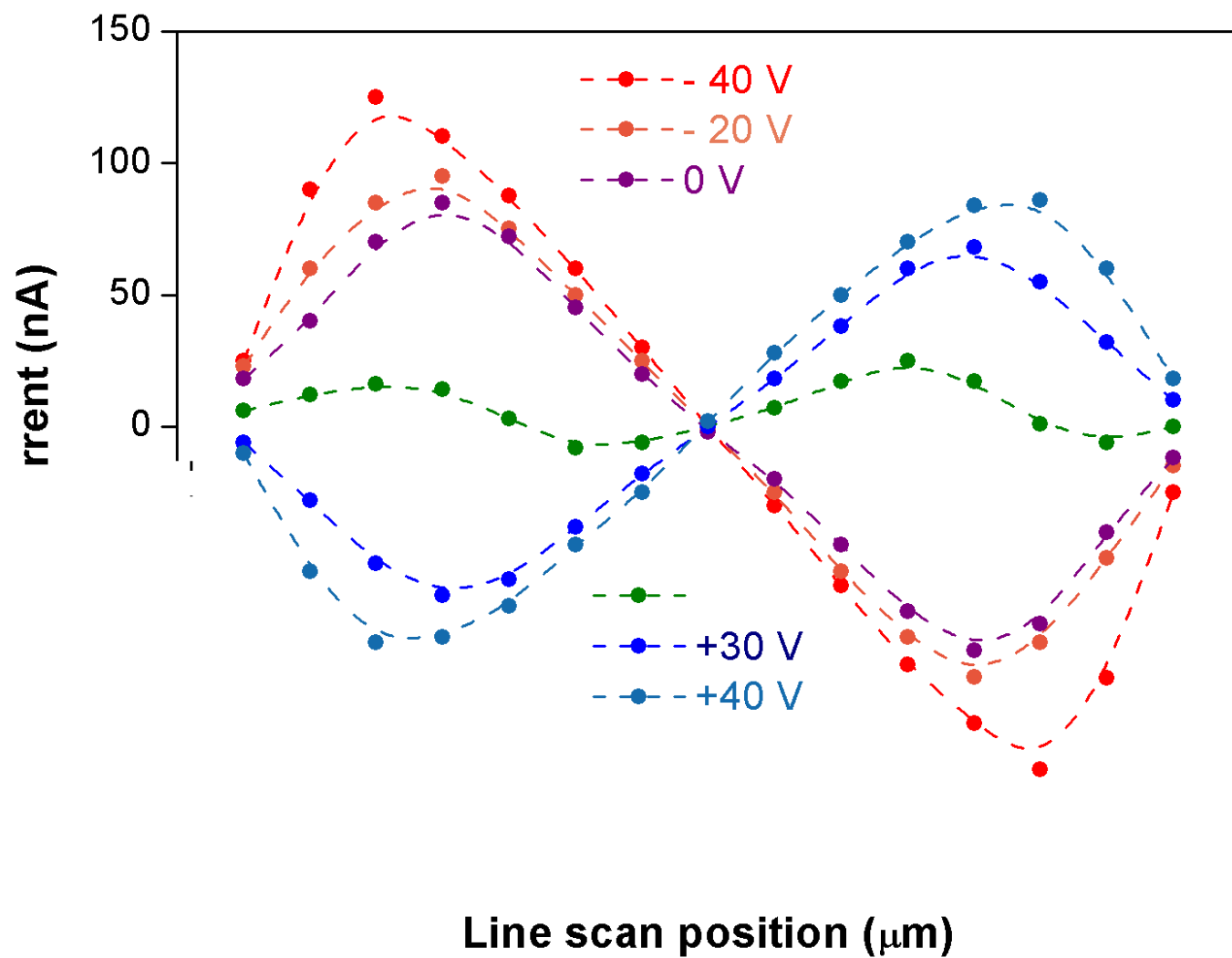
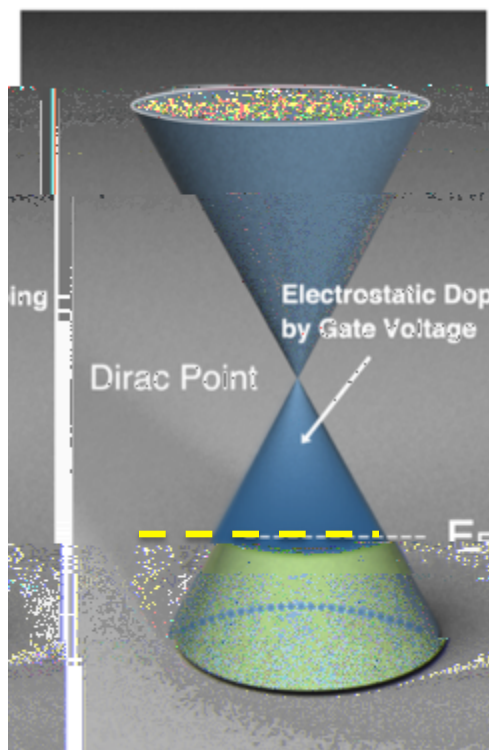
Photocurrent Detection



Polarization Dependence

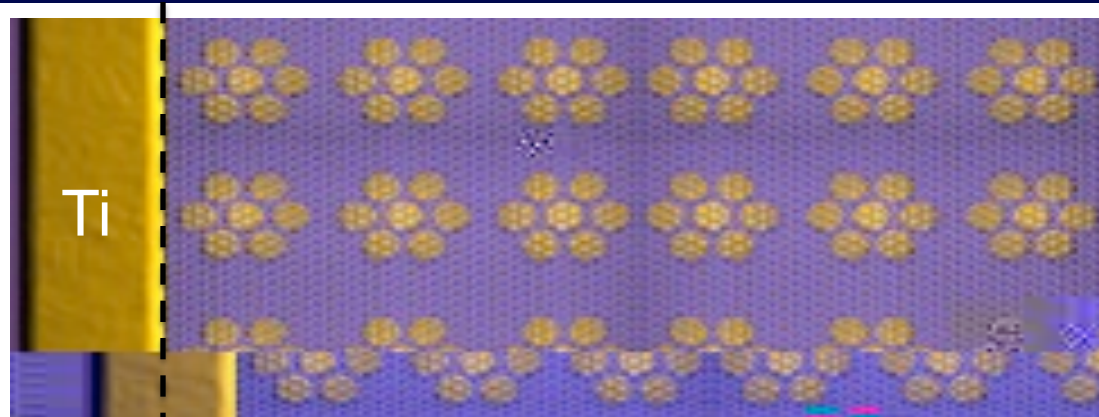


By choosing a different geometry, we can make either polarization dependent or independent photodetector

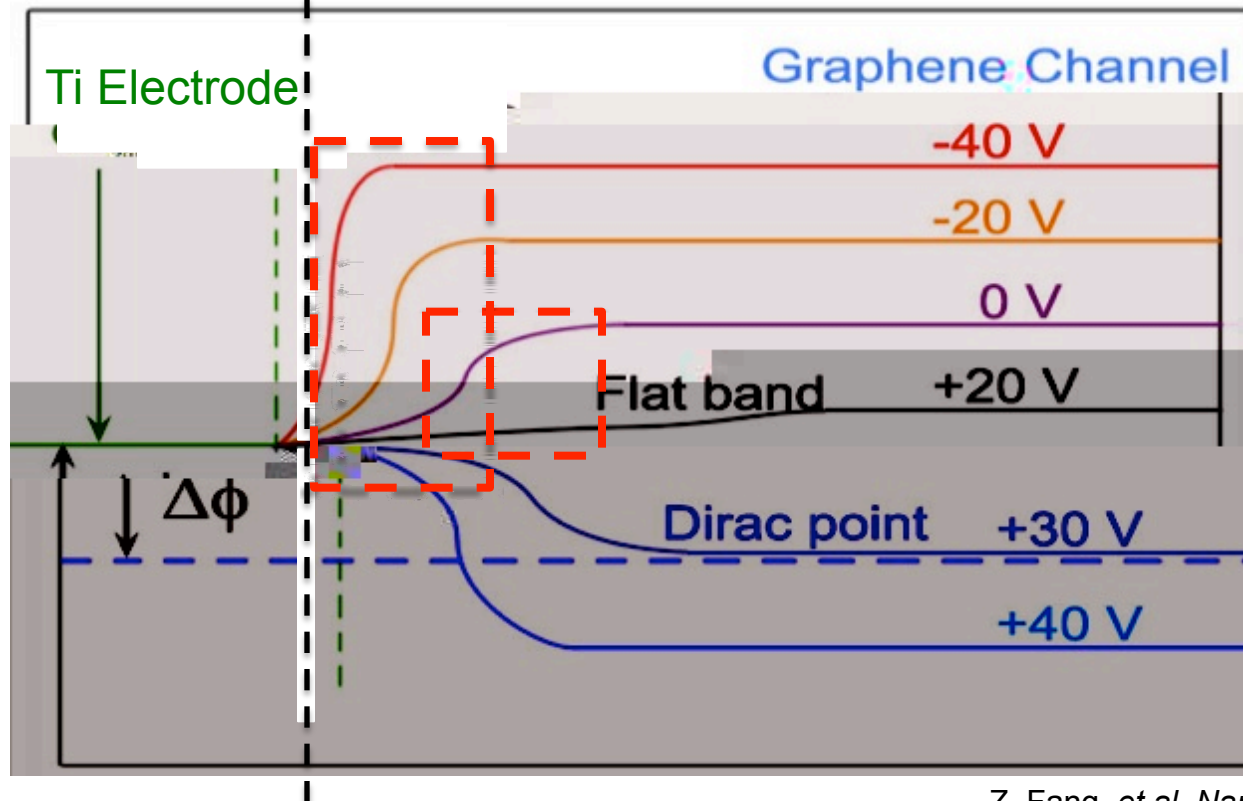


Gate Voltage Control

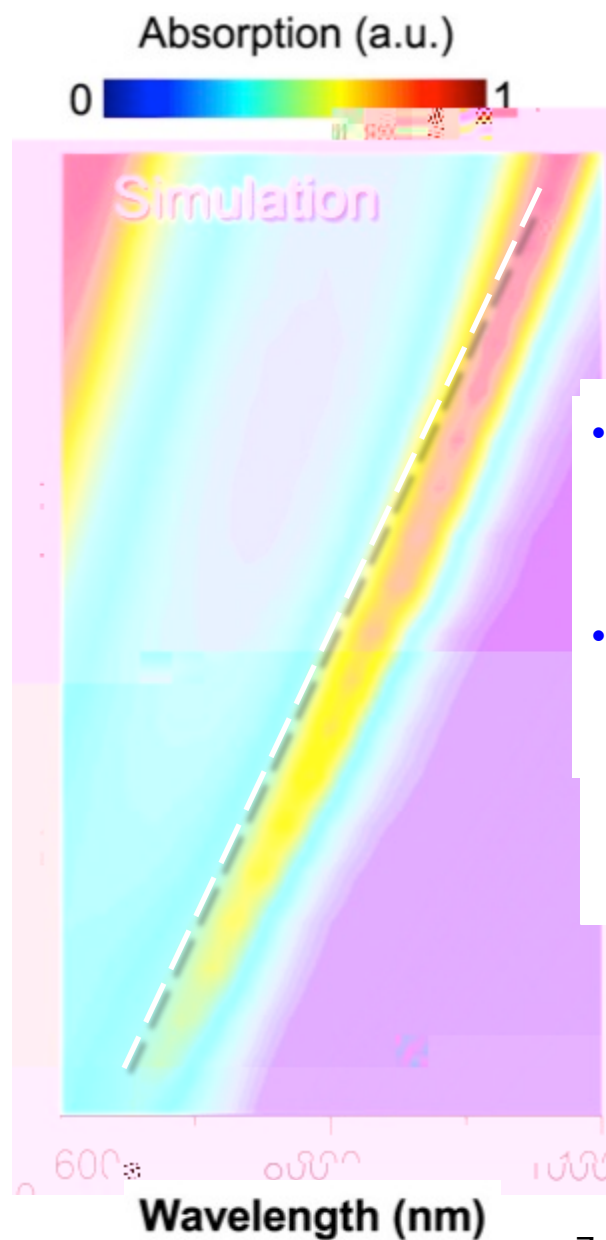
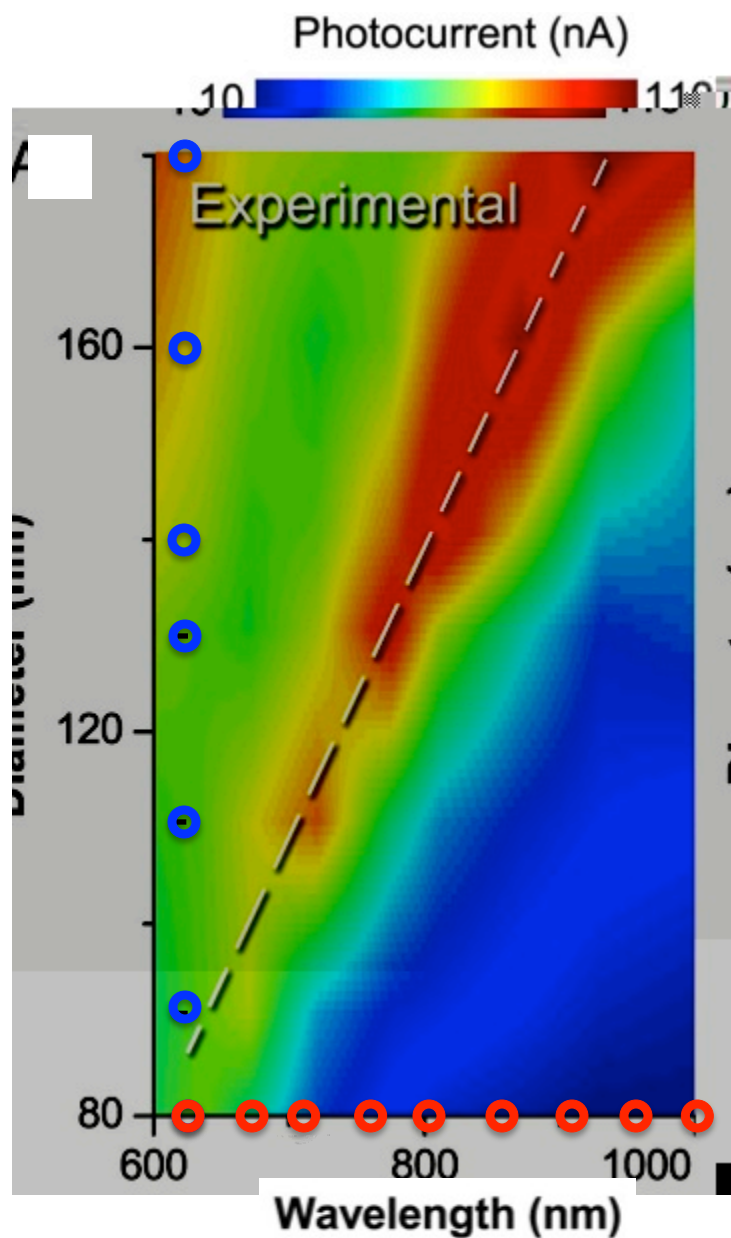
Source
Electrode



Surface
Potential
Diagram

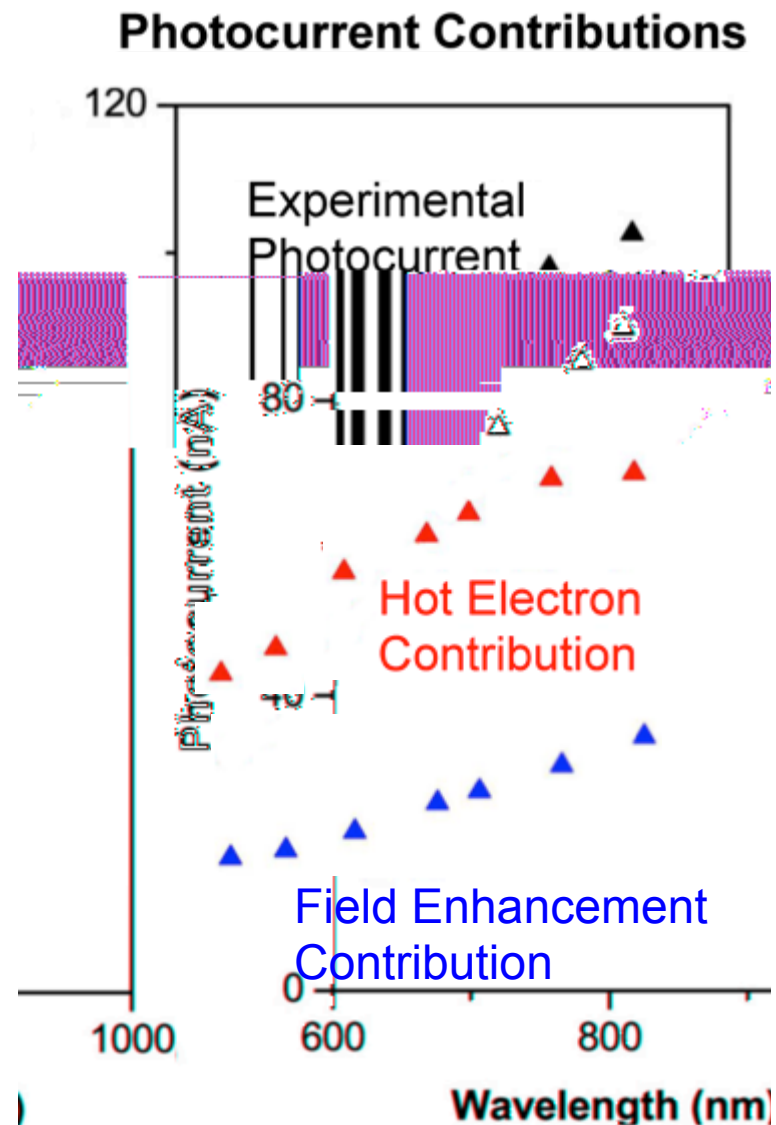
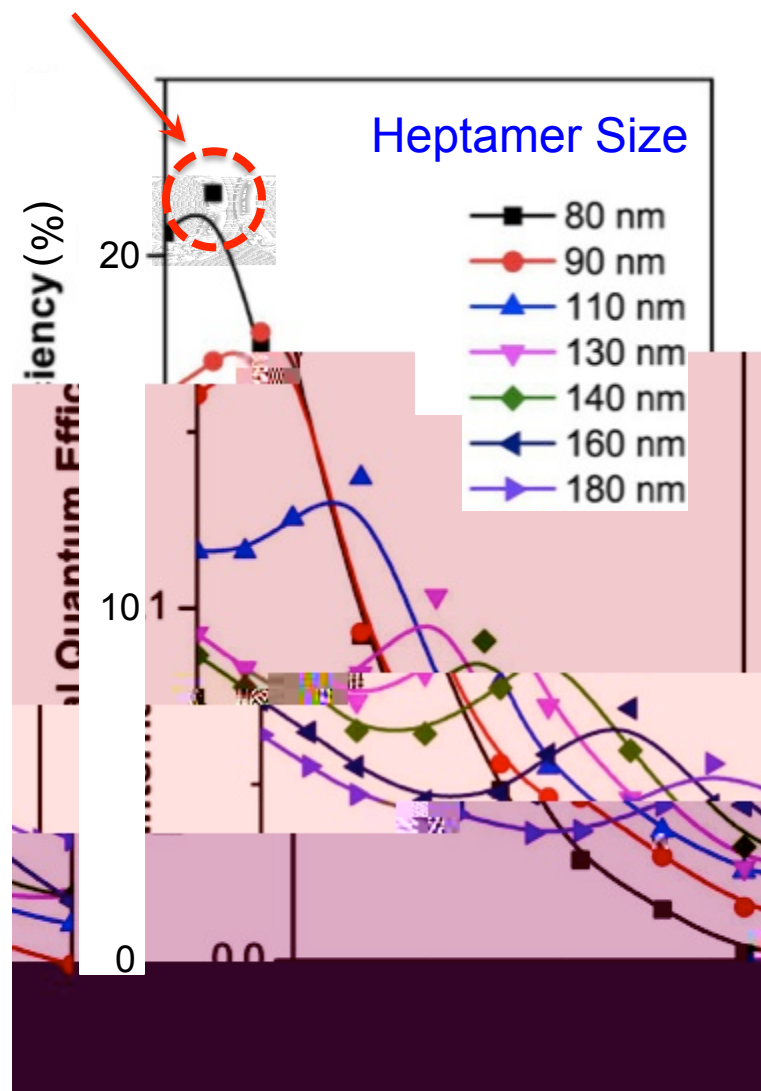


Selective Resonance Detection



- Realize the tuning of resonance wavelength from visible to NIR
- Have a good agreement between the simulation and experiment

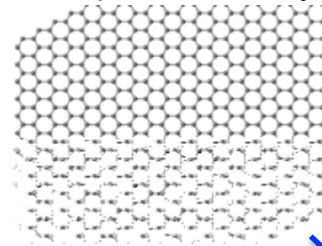
Internal Quantum Efficiency



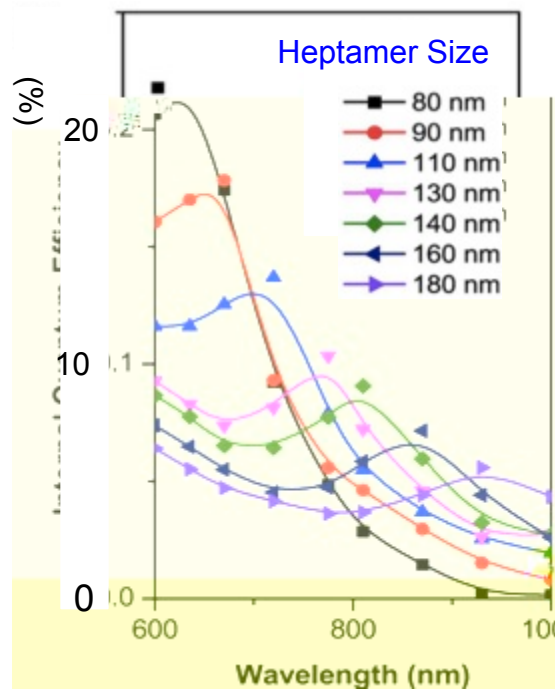
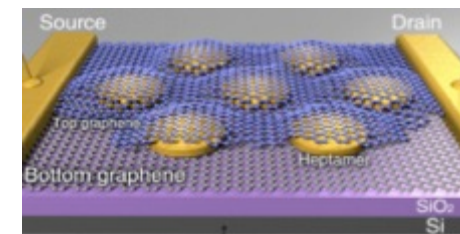
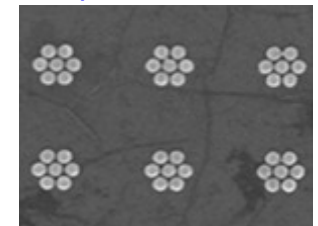
Summary: graphene photodetector

Fabricate antenna between two monolayer graphene, maximize signal from the whole k -space

Graphene Monolayer

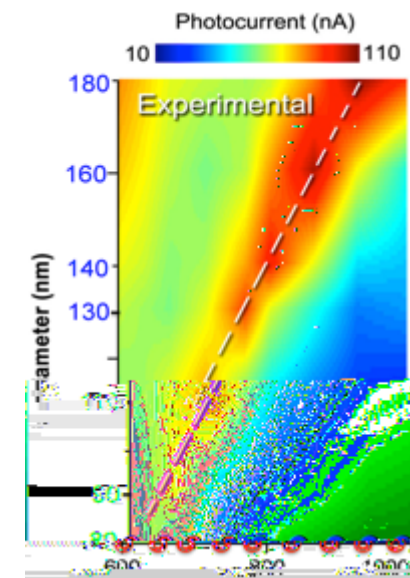


Heptamer Antenna



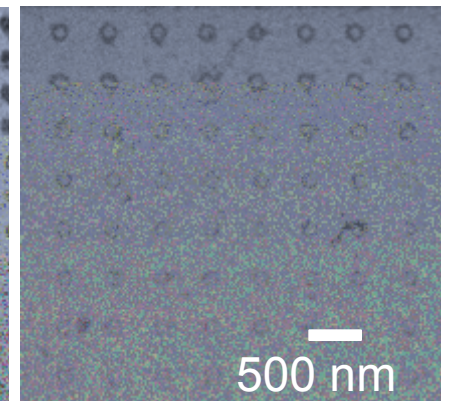
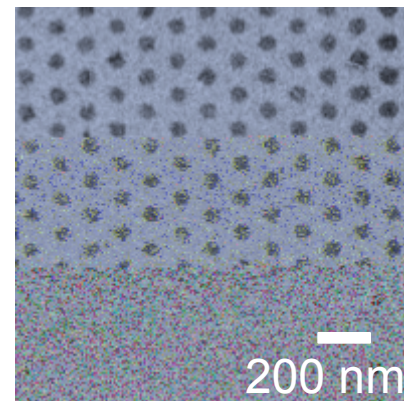
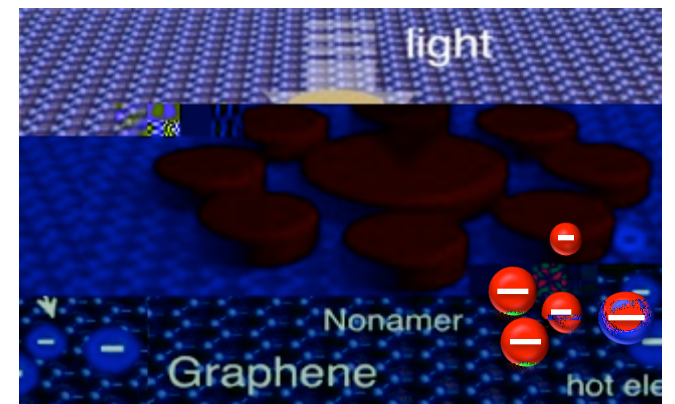
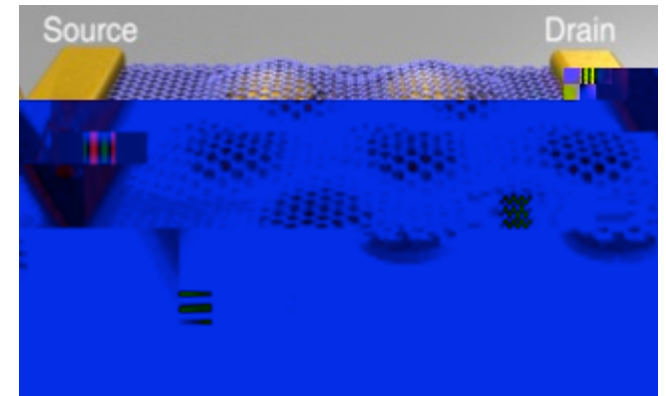
800% photocurrent enhancement,
20% internal quantum efficiency!

C : polarization, size, resonance frequency
(visible to near infrared), gate voltage tuning

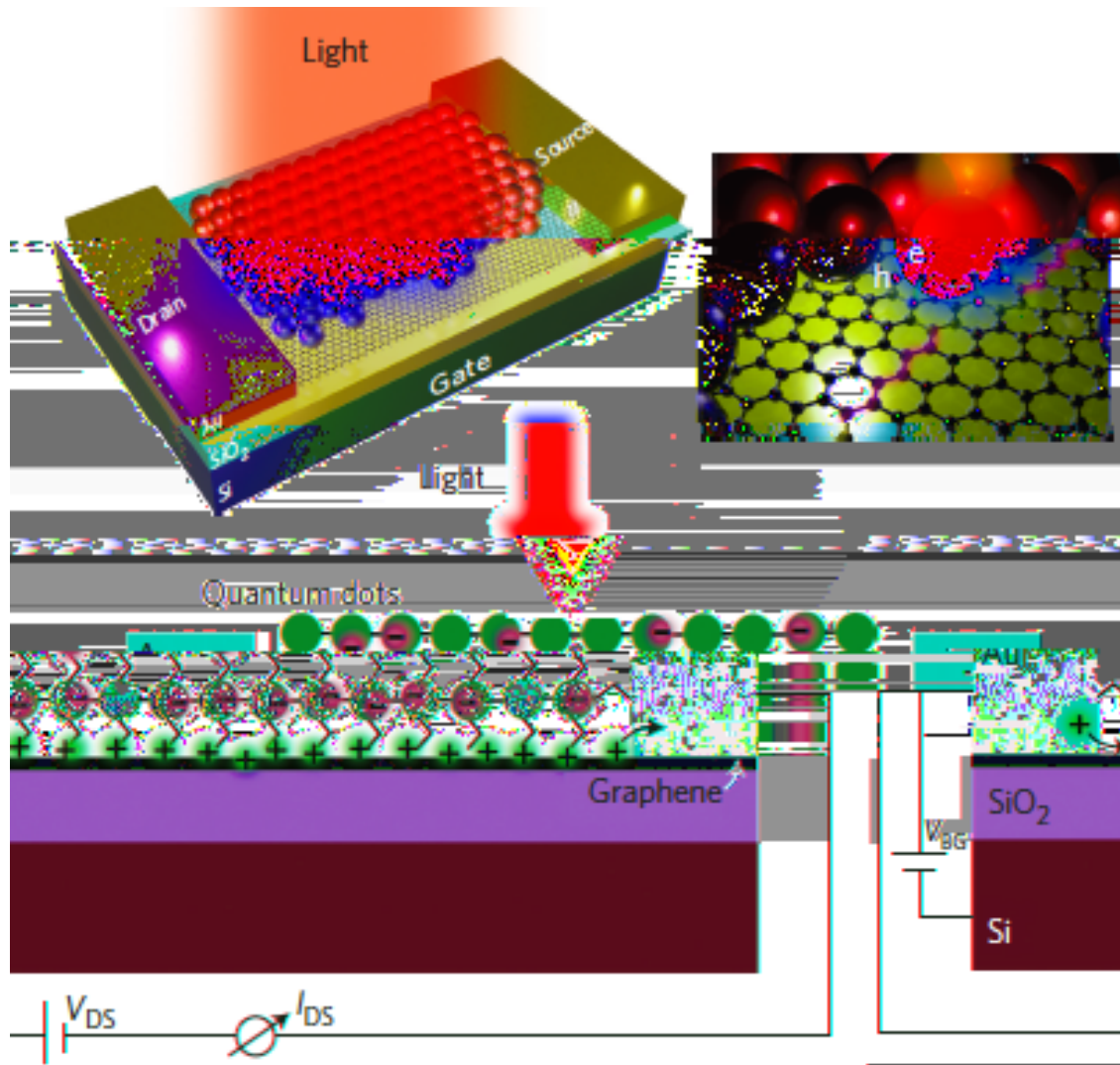


Outline

- Graphene-antenna sandwich photodetector
- Doping graphene with plasmonic hot electrons
- Graphene nanostructures
 - nanodisk
 - nanoring



Hole doping graphene

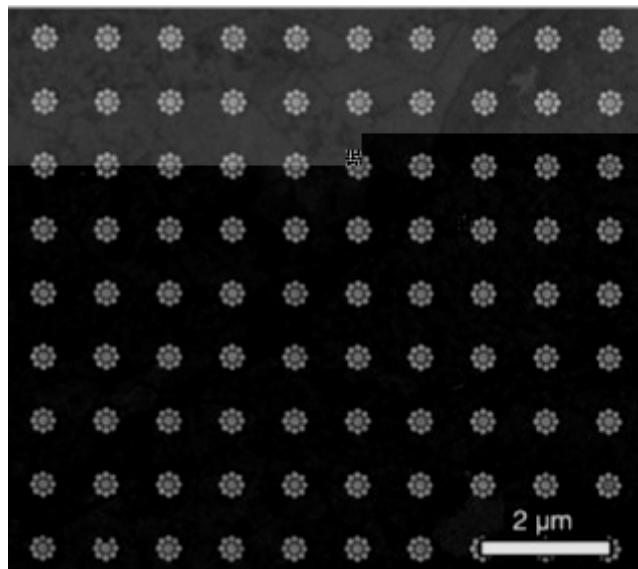
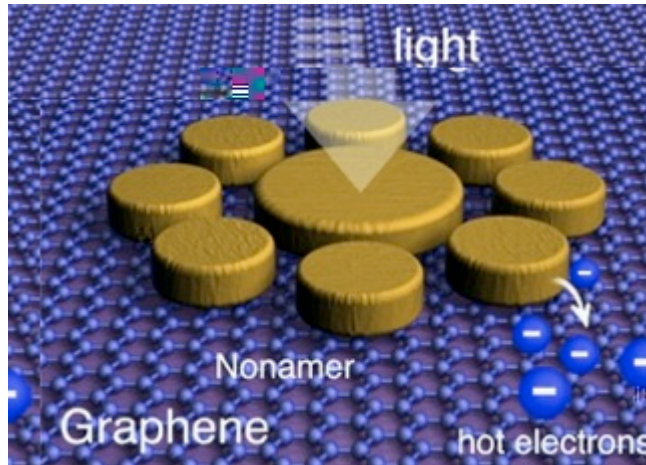


p-type doping
graphene with
quantum dots

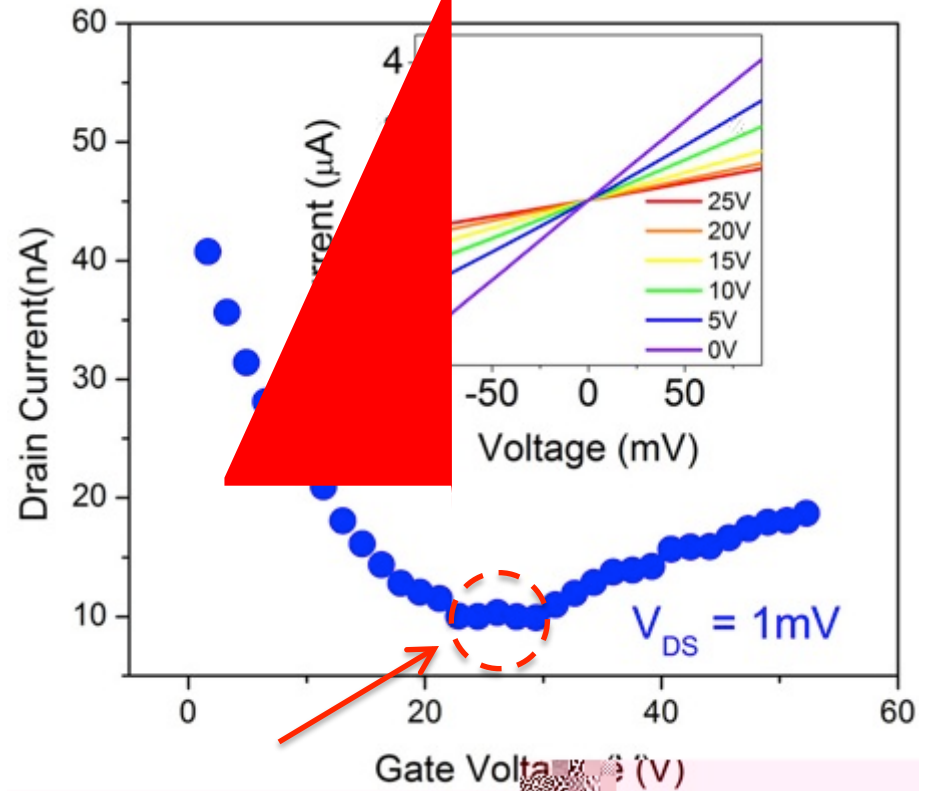
Hole injection!

Can we realize
n-type doping
graphene by
plasmonic hot
electrons?

Graphene-Antenna Device



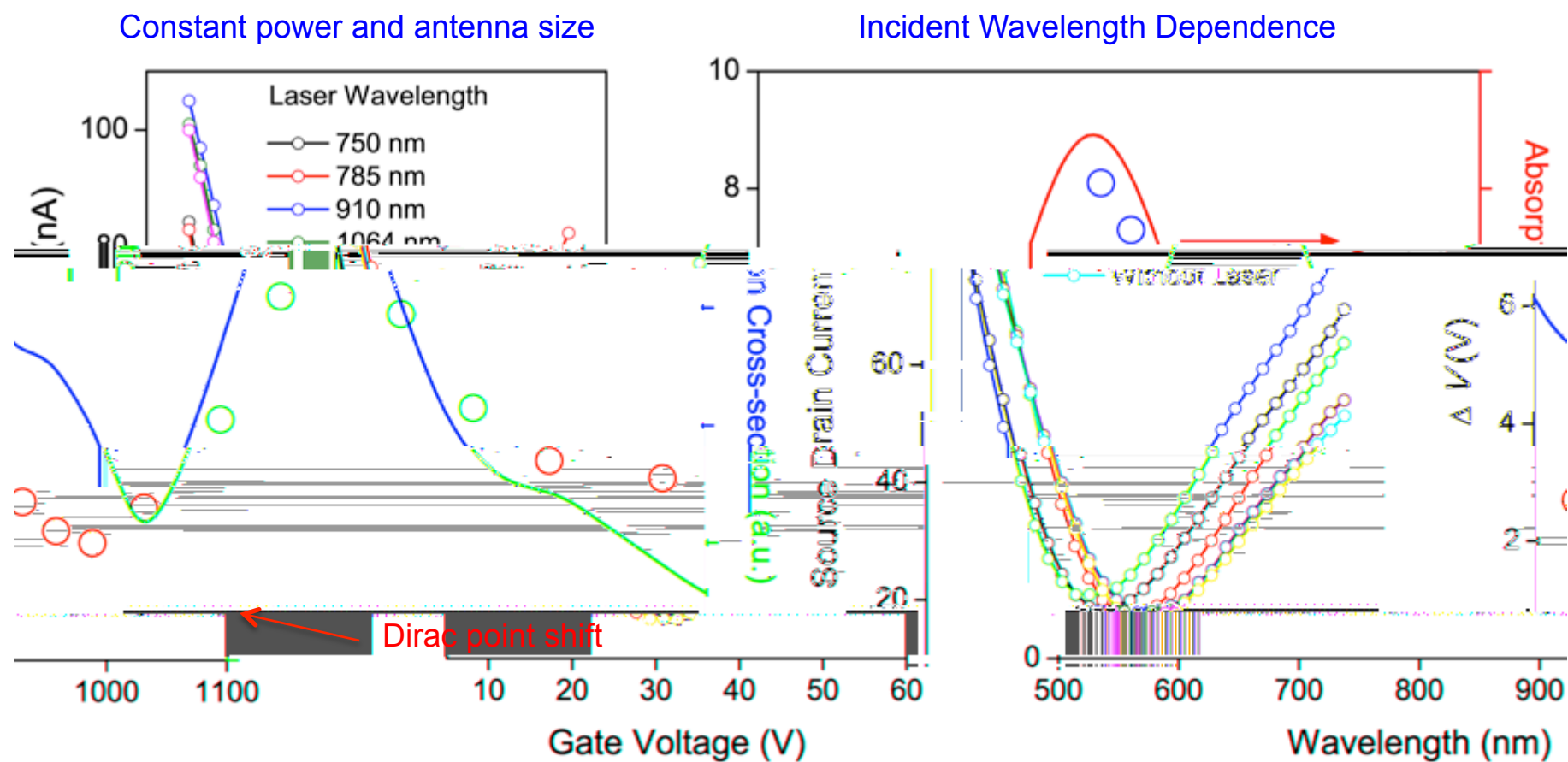
_____ image for the nonamer
fabricated on graphene using E-beam
lithography



C

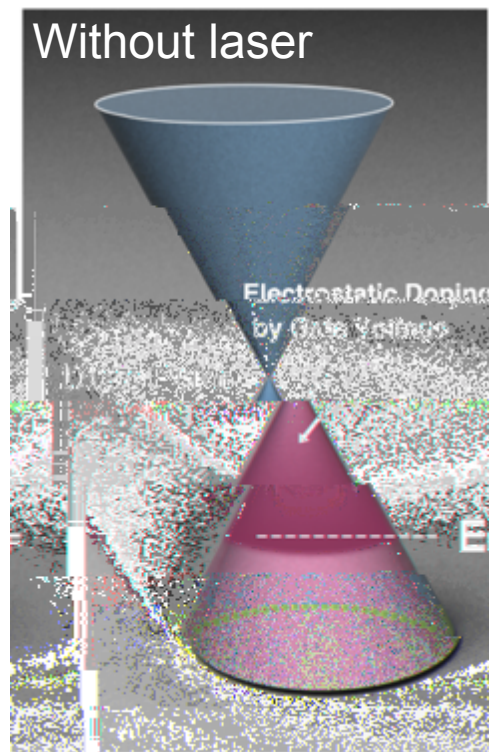
at a source-drain bias of 1 mV
Inset: I - V plots for various gate
voltages V_G from 0 to 60V

Dirac point shift with absorption

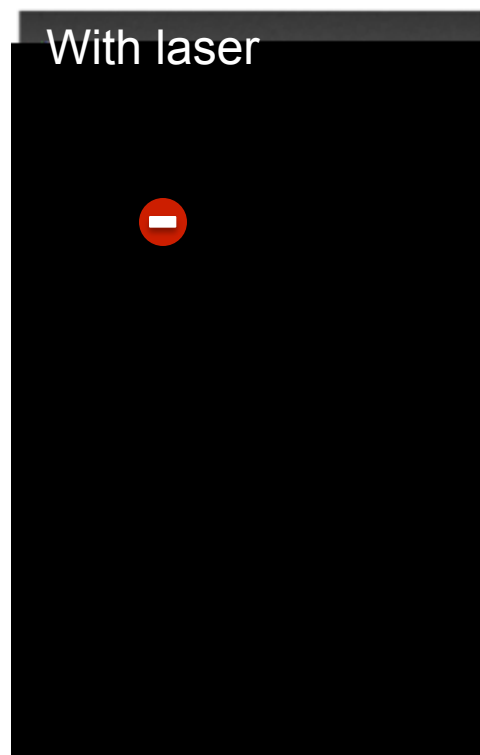


- Electrical transport characteristic (I - V_G curves) of the nonamer antenna-graphene phototransistor

Dirac point shift with absorption



$$N_{ES} = Q/e = C_g V/e$$

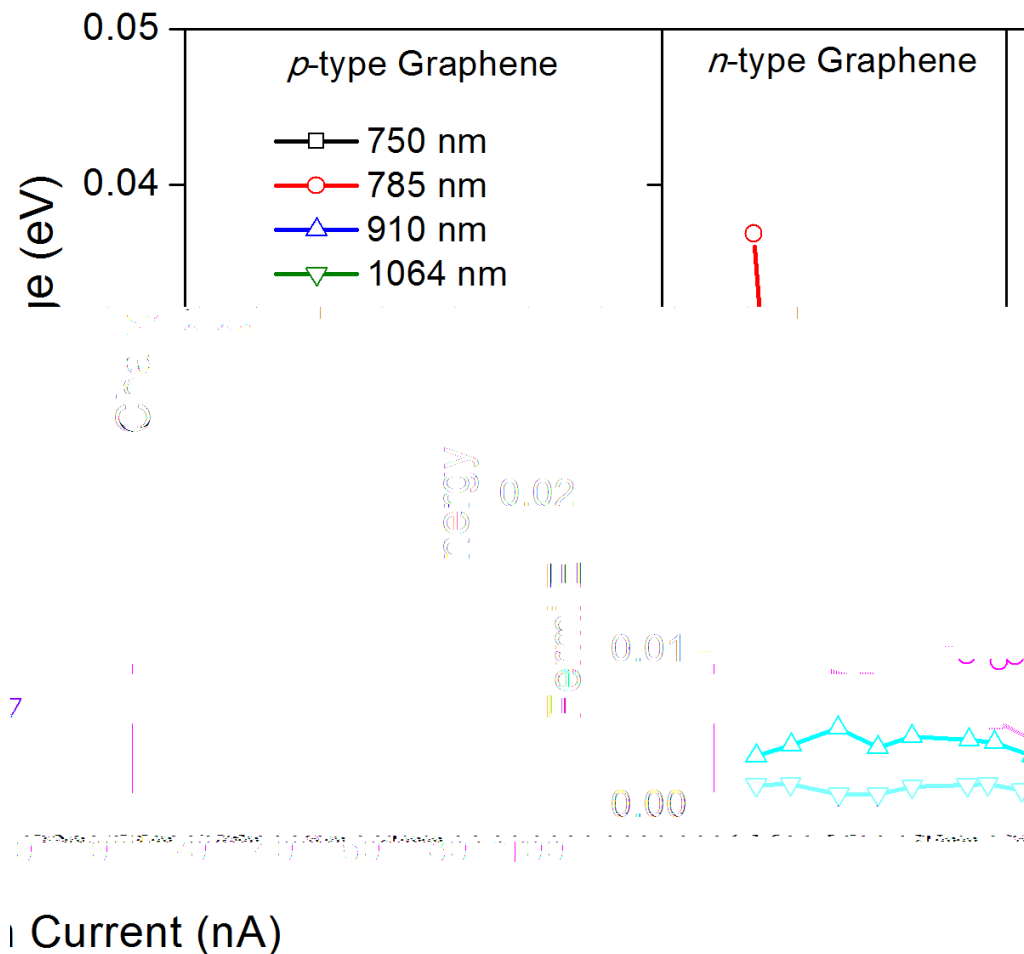
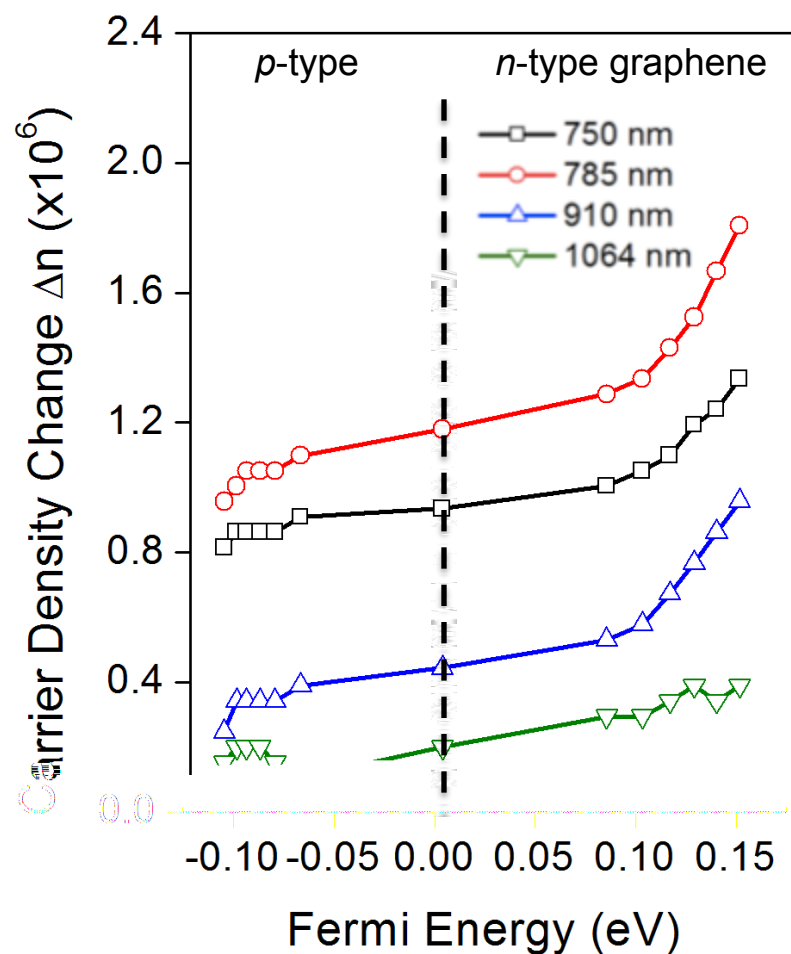


$$N = N_{ES} + N_{HE} = C_g V'/e + \alpha N_{HE}$$

The recorded Dirac point shift $\Delta V = |V - V'|$ is proportional to the nonmagnetic absorption cross-section $\Delta V \propto \sigma_{abs}$

$$E_F = \hbar v_F \sqrt{|C_g (V_g - V_D) / eA|}$$

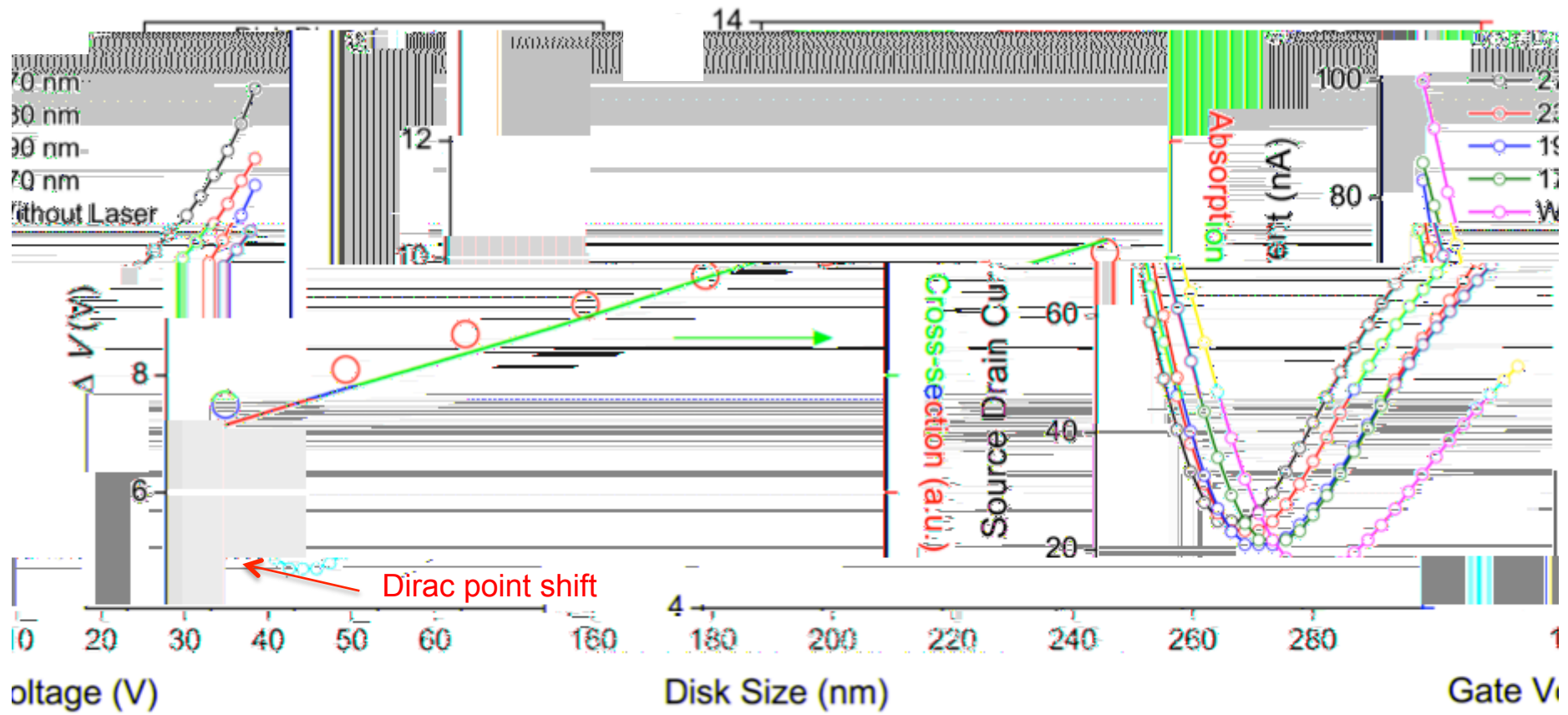
Dirac point shift with absorption



- Dependence of E_F with photogenerated carrier density change
- Dependence of Source-drain current on photogenerated E_F change

Antenna size control

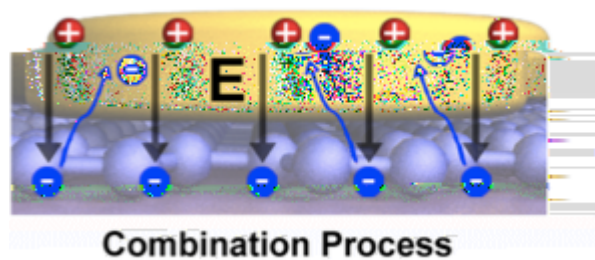
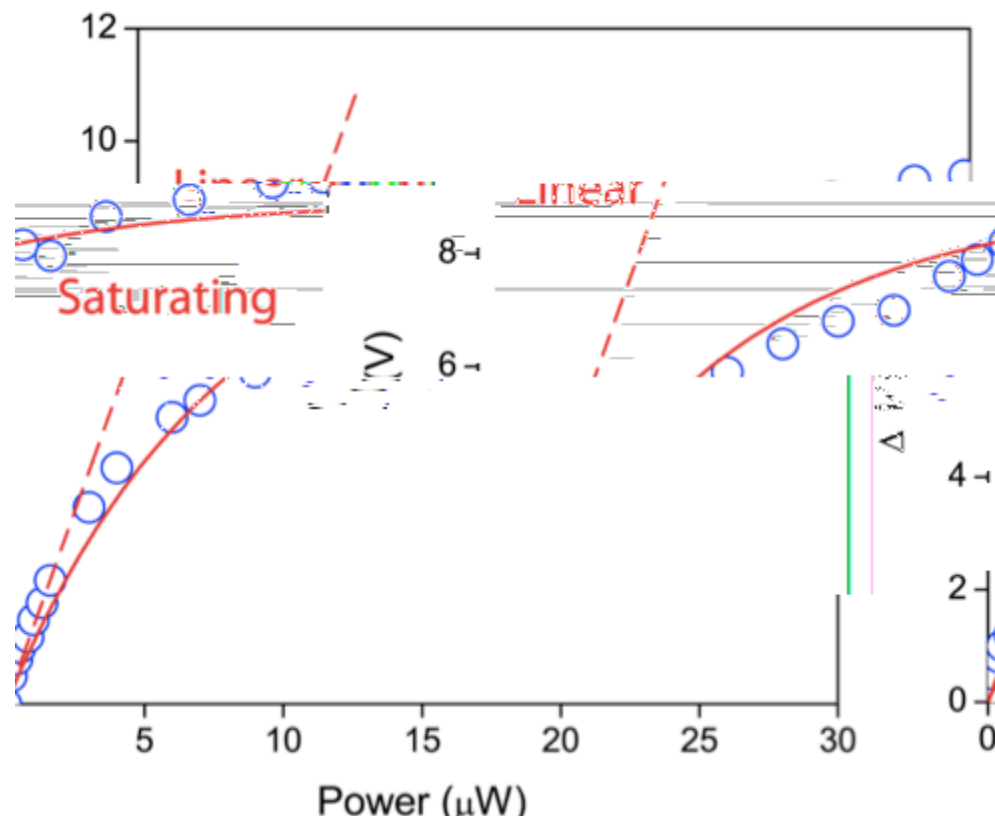
Constant laser wavelength (785 nm) and power



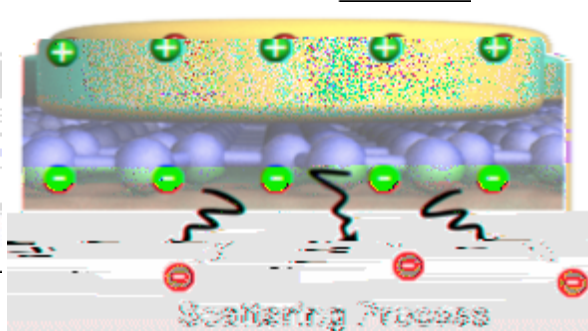
- I - V_G curves for different sized nanowire array
- Dirac point shift data and the fitting curve simulated from structure absorption

Hot electron recombination and scattering

Constant laser wavelength and antenna size



Combination Process



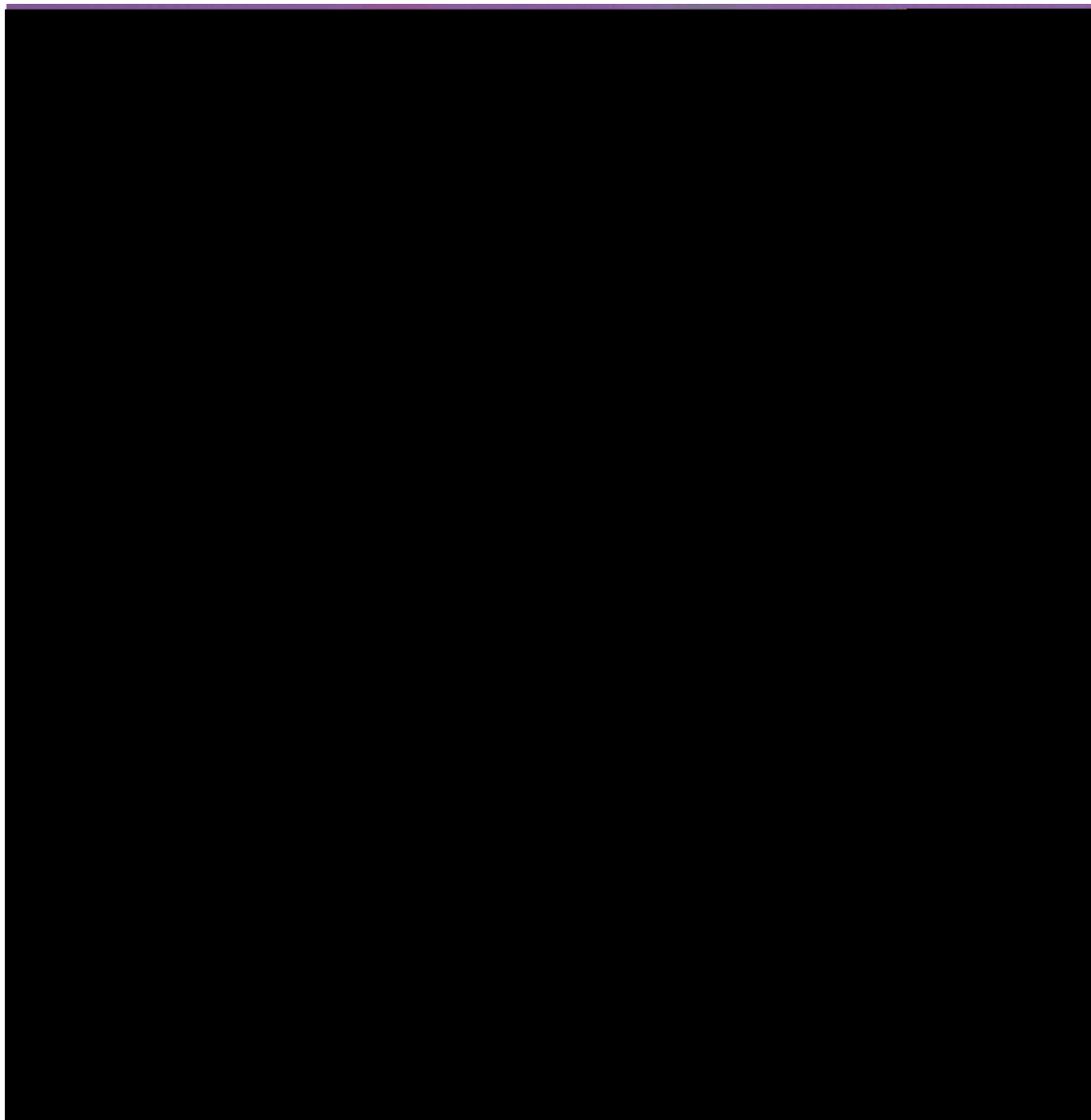
Scattering Process

The internal electrostatic field drives a portion of the electrons back to the antenna

Injected hot electrons with the excessive electrons in graphene induced by Coulombic interactions

estimated as 10^{-6} s for the case $\Delta V = 4$ V (under 5 μ W incident laser power)

Optical Induced Circuitry



Optical Induced graphene
p-n junction

Optical Induced graphene
n-p-n transistor

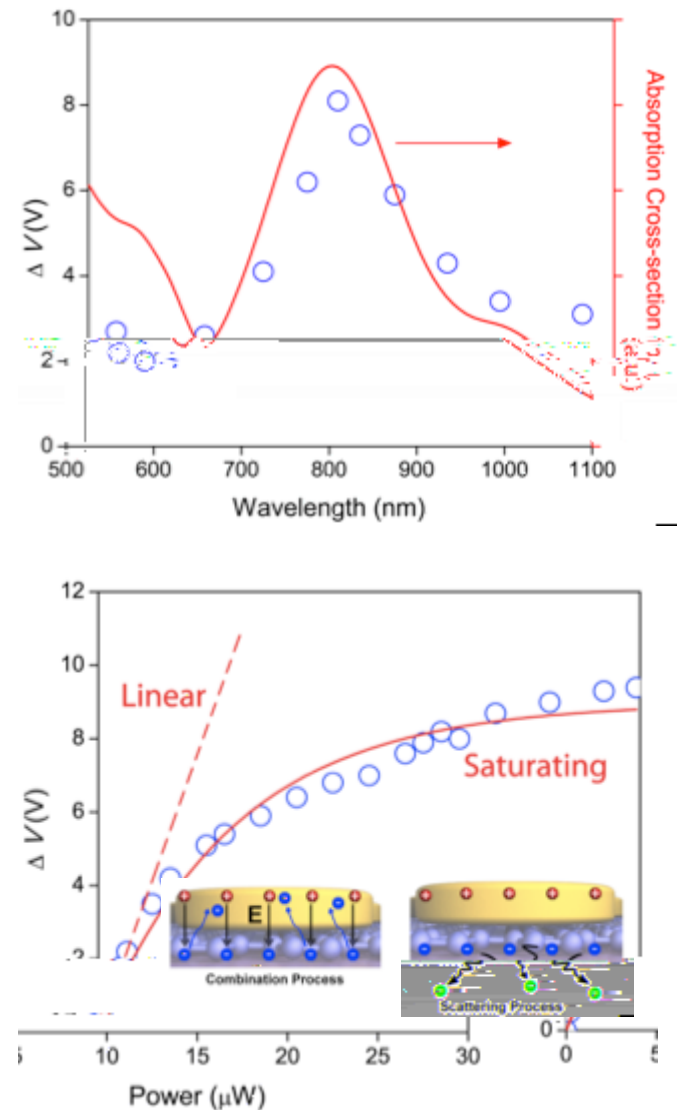
Summary: hot electron doping graphene

Different incident laser, antenna size, and incident laser power

Hot electron recombination in Au antenna, and electron scattering in graphene

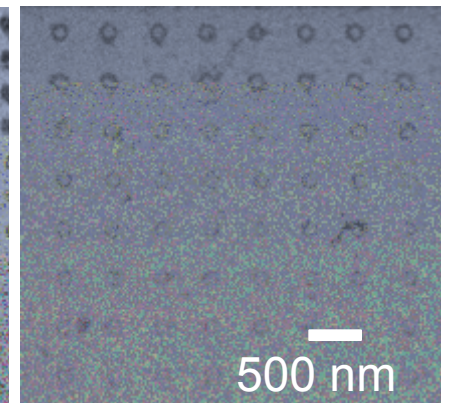
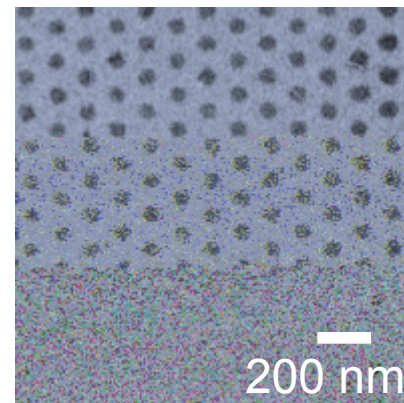
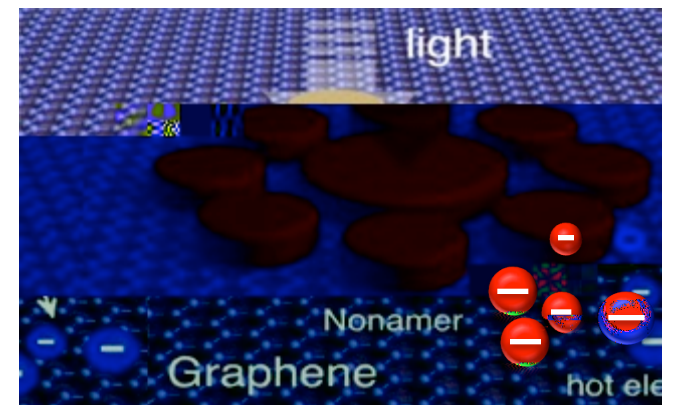
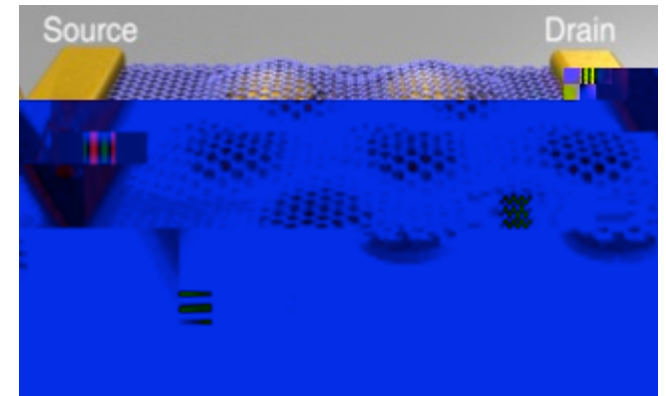
Hot electron doping (10^{-6} s) is much faster than *p*-type doping by using quantum dots

p-n junction;
n-p-n transistor

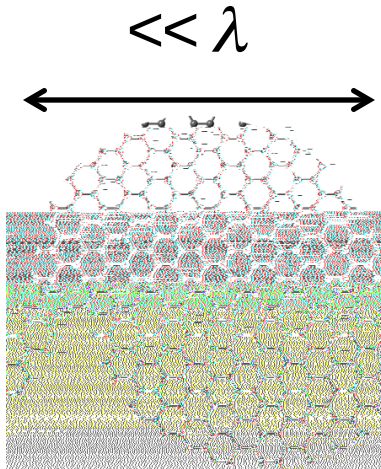


Outline

- Antenna-enhanced graphene sandwich photodetector
- Plasmonic hot electrons doping graphene
- Graphene Nanostructures
 - nanodisk
 - nanoring



Graphene nanodisk: plasmonic dipolar mode

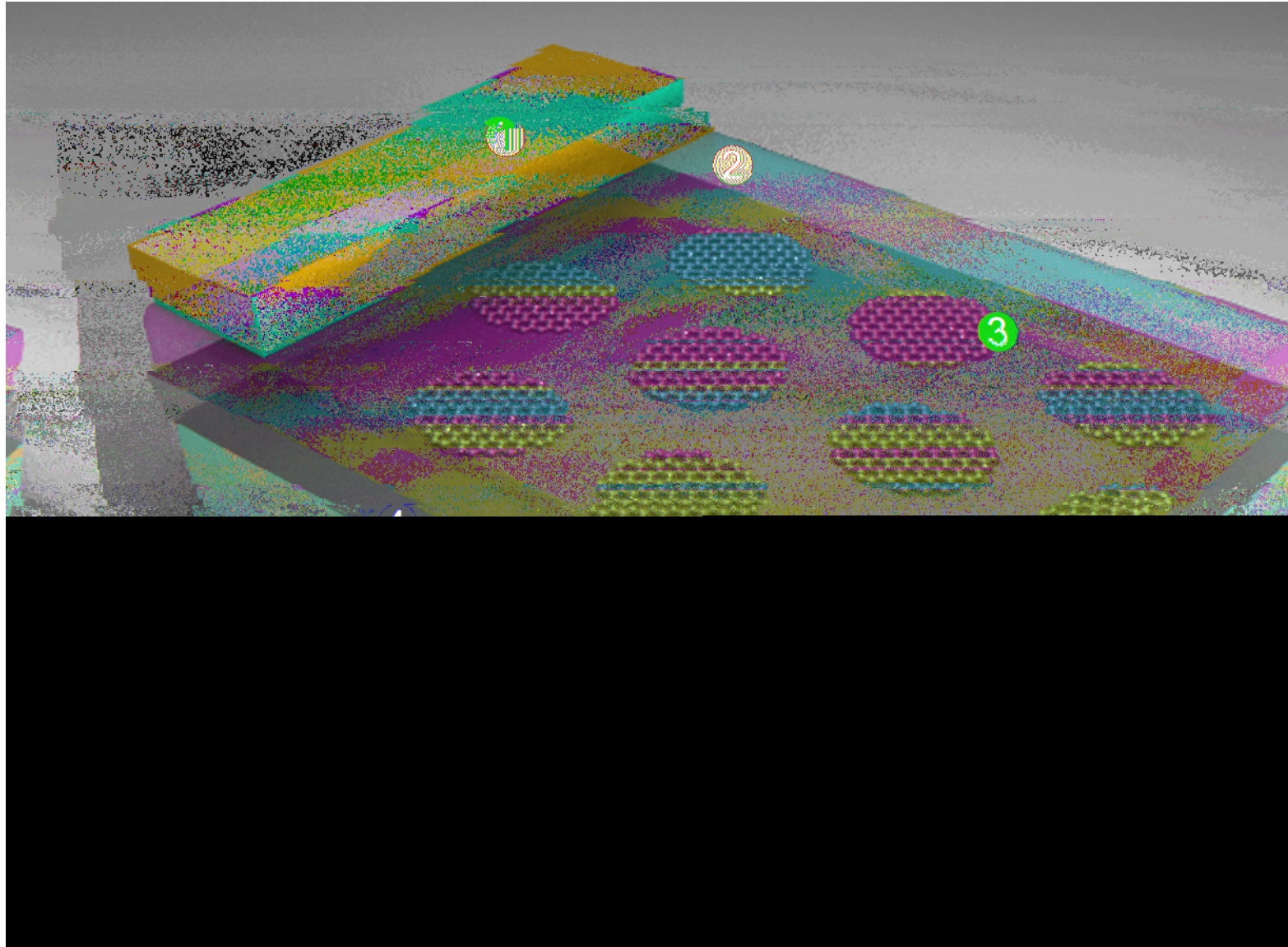


$$\alpha = \frac{3c^3}{4\omega^3} \frac{\kappa_r}{\omega_p - \omega - i\kappa/2}$$

$$\sigma^{\text{ext}}(\omega) = \frac{4\pi\omega}{c} \text{Im}\{\alpha\} \approx \frac{3\lambda^2}{2\pi} \frac{\kappa_r}{\kappa}, \quad \kappa_r \ll \kappa$$

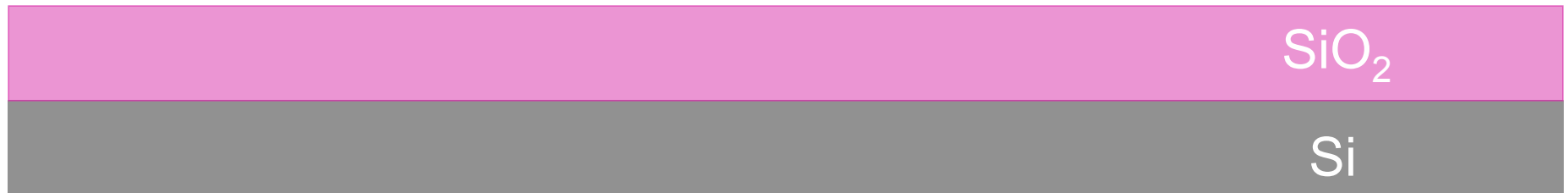


Device Schematic



Ion Gel Top Gating Method

Start with SiO_2 substrate



Ion Gel Top Gating Method

Deposit ITO layer



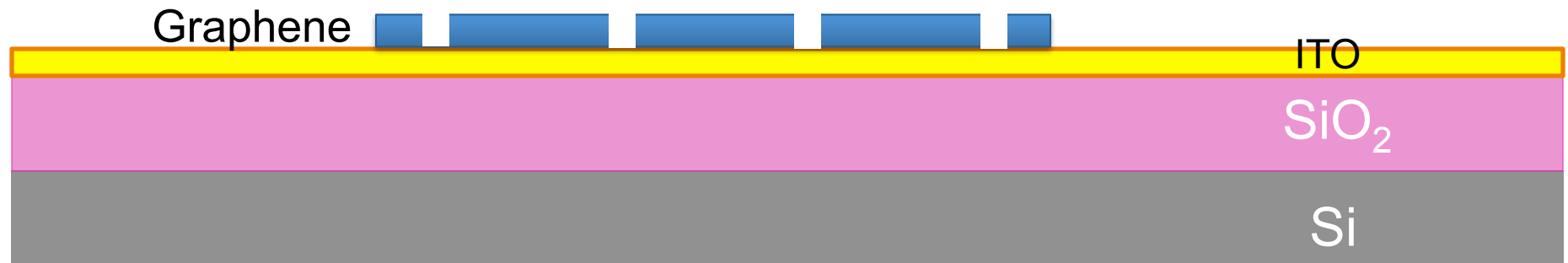
Ion Gel Top Gating Method

Transfer Graphene Monolayer



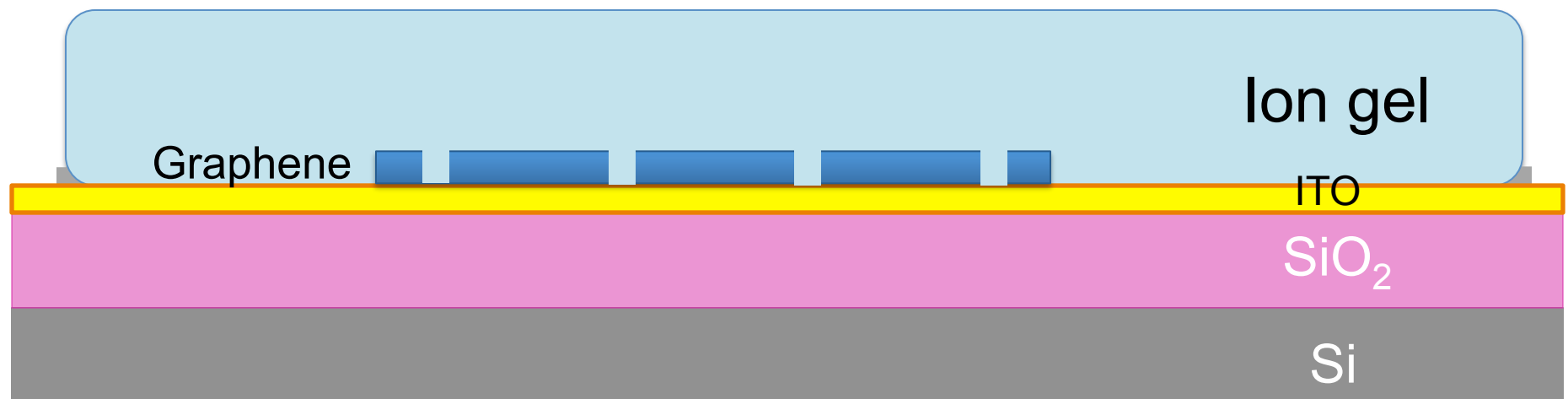
Ion Gel Top Gating Method

Pattern graphene with nanodisk array



Ion Gel Top Gating Method

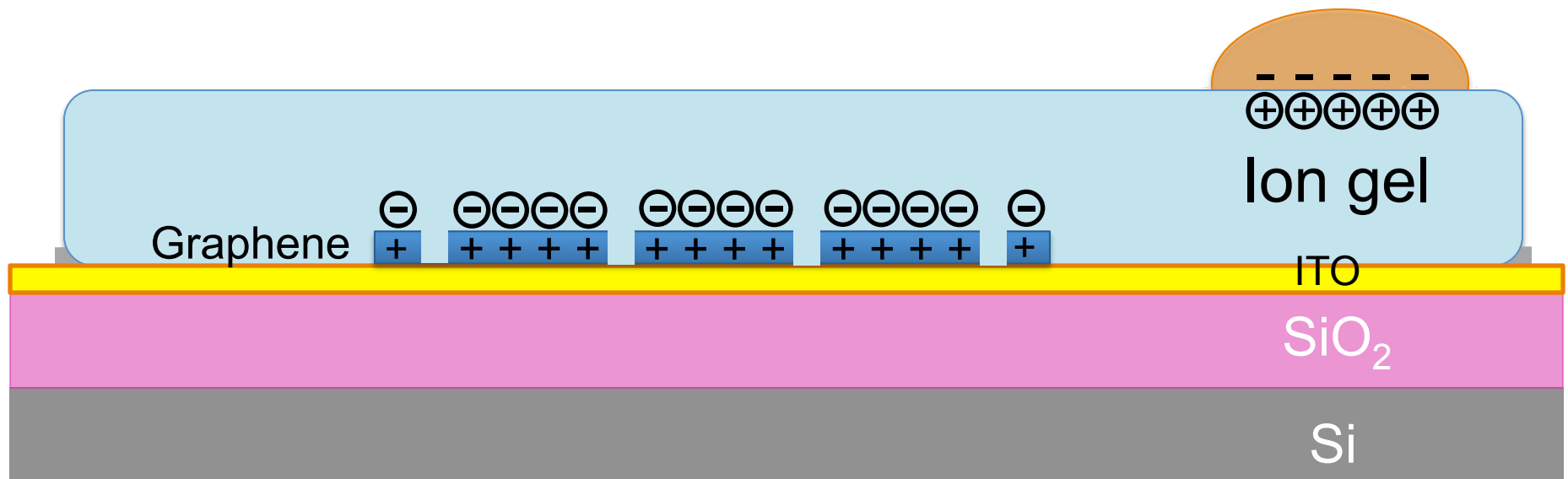
Spin-coating Ion gel



Ion Gel Top Gating Method

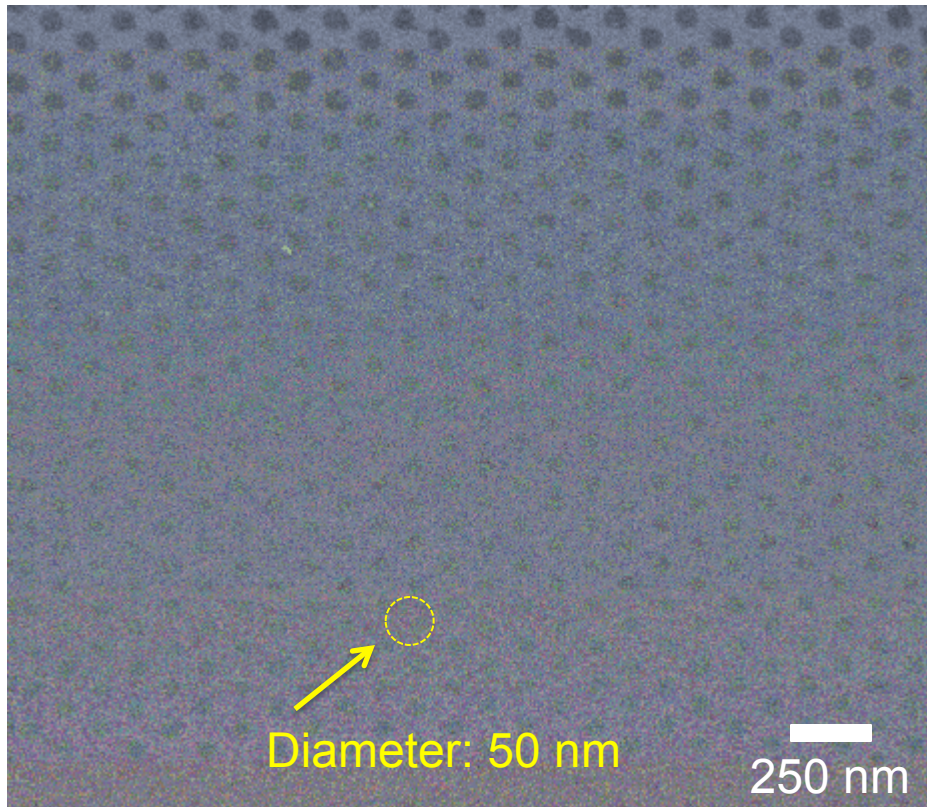
Apply gate voltage

Top Gate Voltage



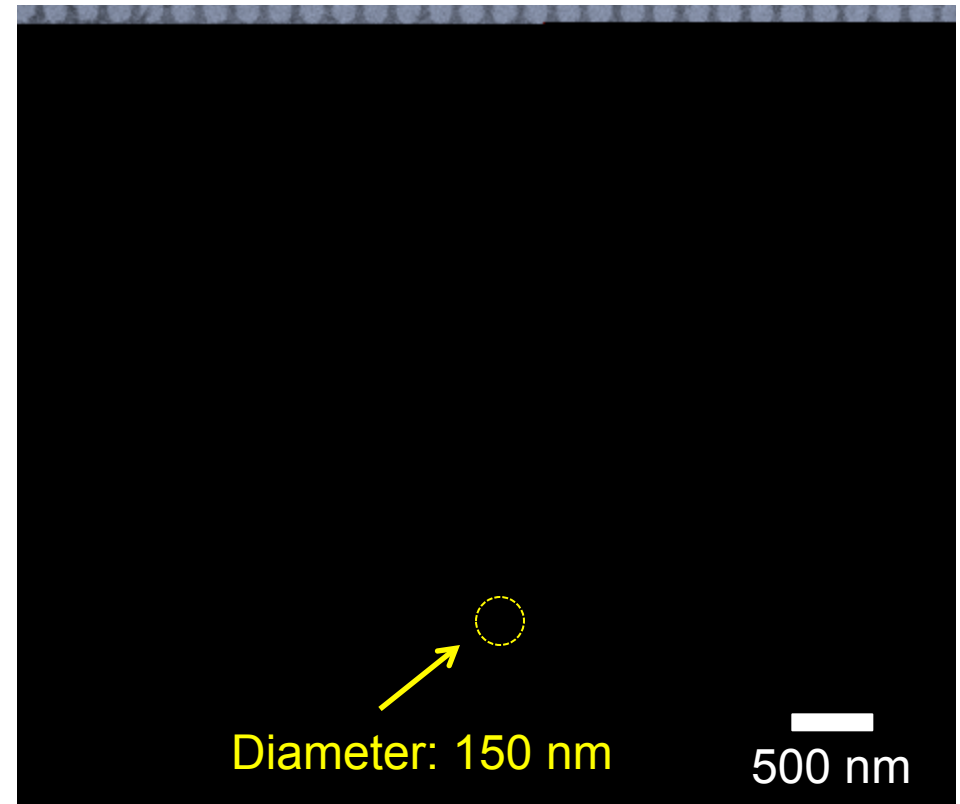
Graphene Nanodisk (D=50 nm) and Nanohole Array

Graphene Nanodisks



Center to center distance: 120 nm
SiO₂ thickness: 285 nm
ITO thickness: 50 nm
Ion gel thickness: 100 nm

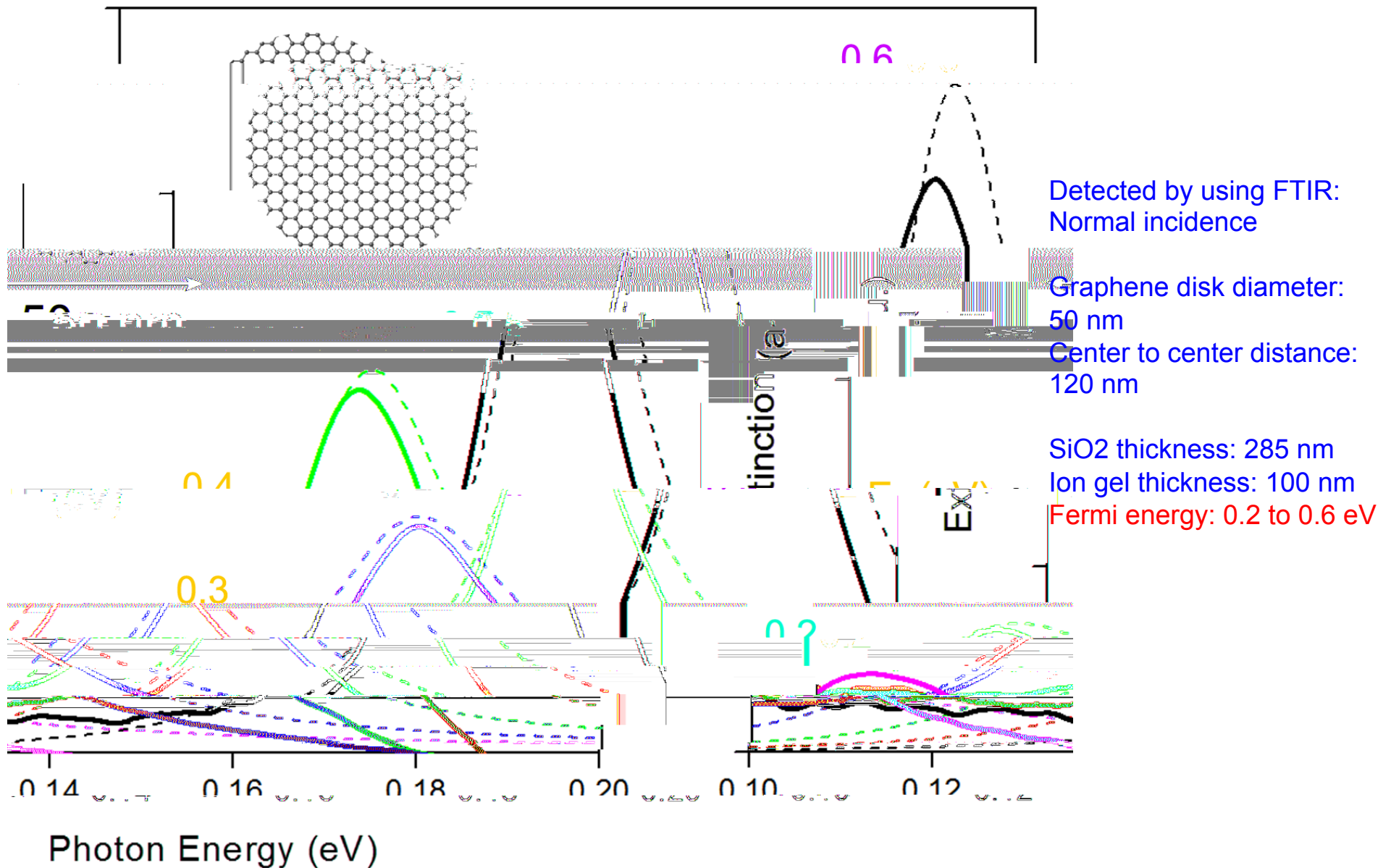
Graphene Nanoholes



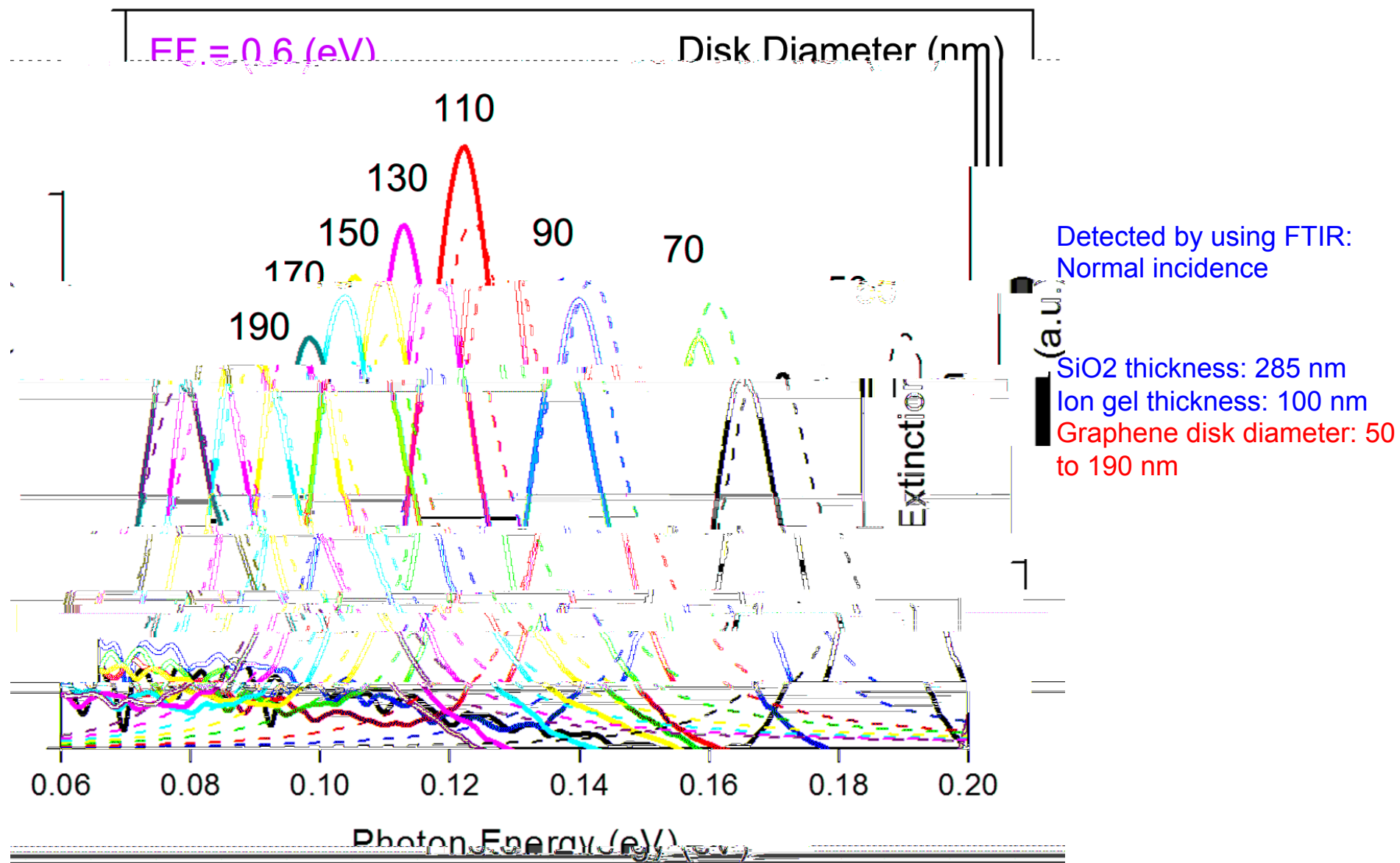
Center to center distance: 250 nm

We can see the graphene wrinkle

Graphene nanodisk plasmon dipolar mode

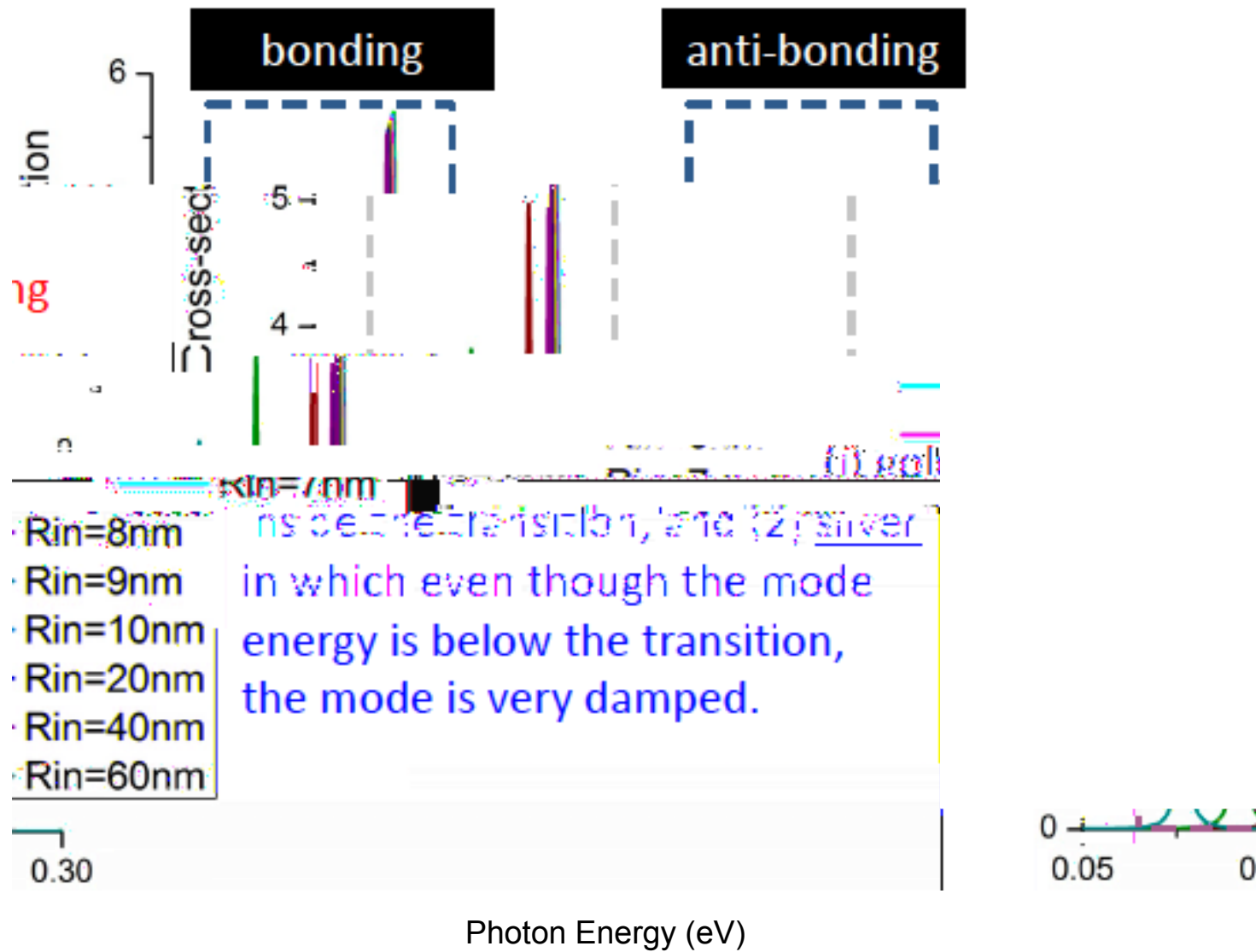


Graphene nanodisk size control

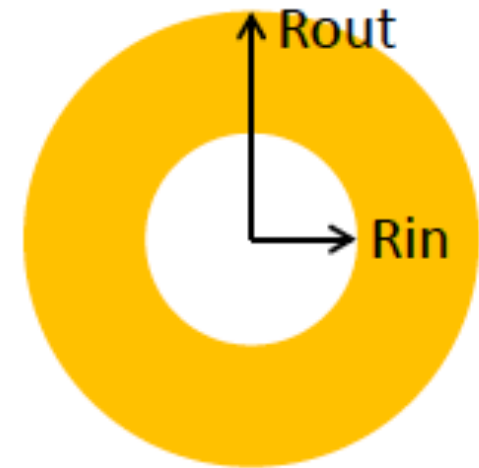
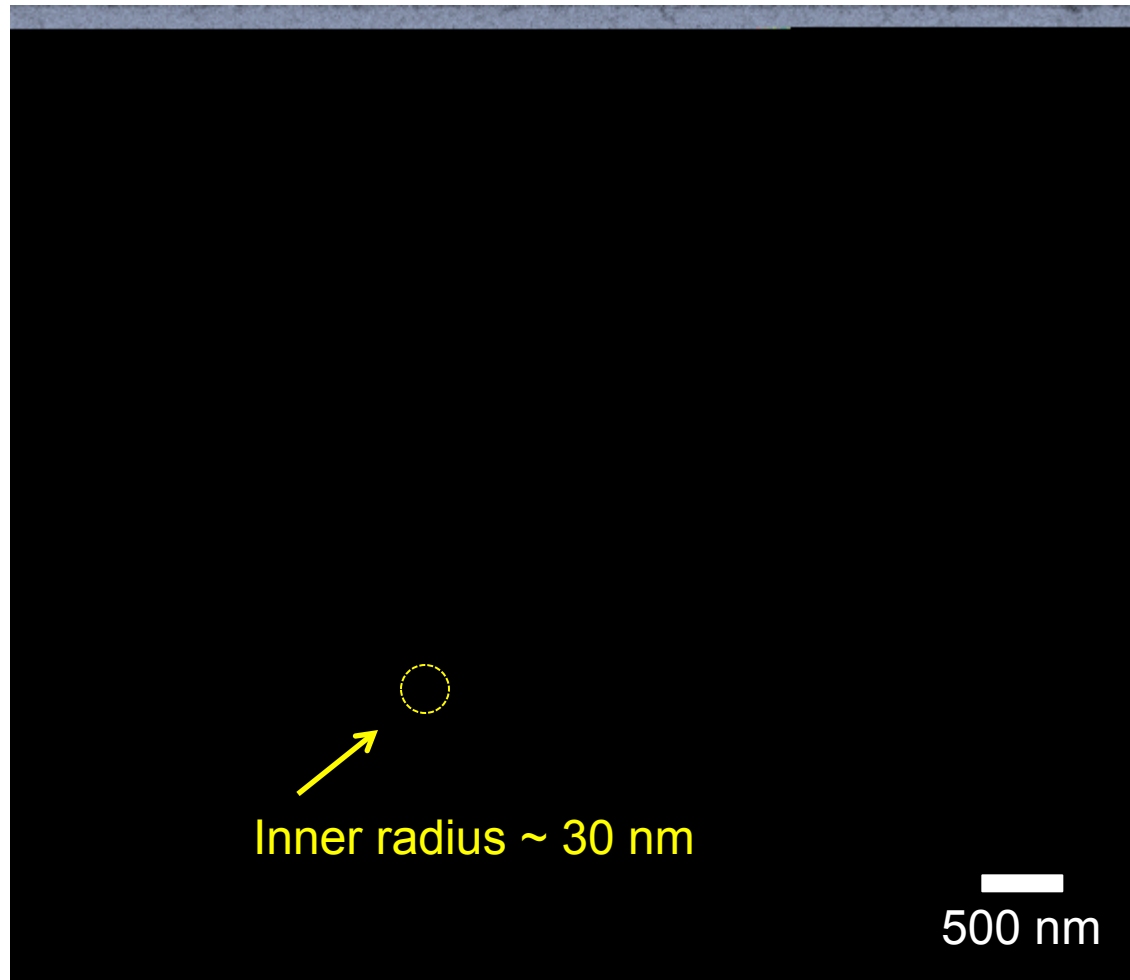




Theoretical Prediction



Graphene Nanoring Structure



$$R_{out} = 50 \text{ nm}$$

$$R_{in} = 30 \text{ nm}$$

$$\text{Period} = 500 \text{ nm}$$

Conclusion

- Graphene-antenna photodetector
 - Sandwich structure
 - high enhancement in visible and NIR
 - High controllable device
- Plasmonic hot electrons doping graphene
 - Incident laser wavelength, power, antenna size
 - Hot electron recombination and further scattering
 - Doping time scale ($10\ \mu\text{s}$)
- Graphene nanostructure
 - Nanodisk plasmonic dipolar resonance
 - Tuning with disk size and Fermi energy
 - Nanoring plasmonic bonding and anti-bonding modes

